



AHEAD OF WHAT'S POSSIBLE™

Mixed-signal technologies for ultra-wide band signal processing systems

GABRIELE MANGANARO

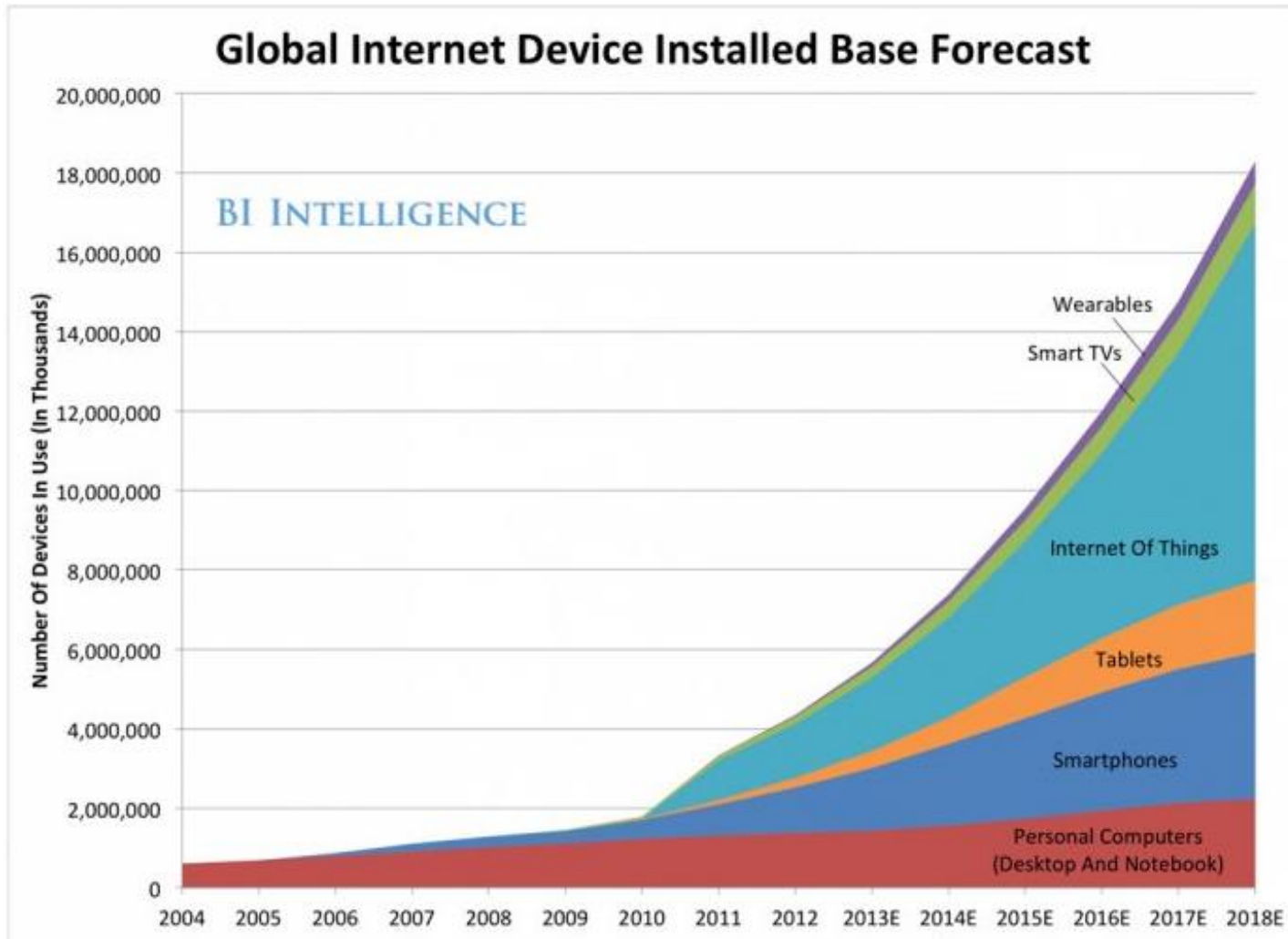


Agenda

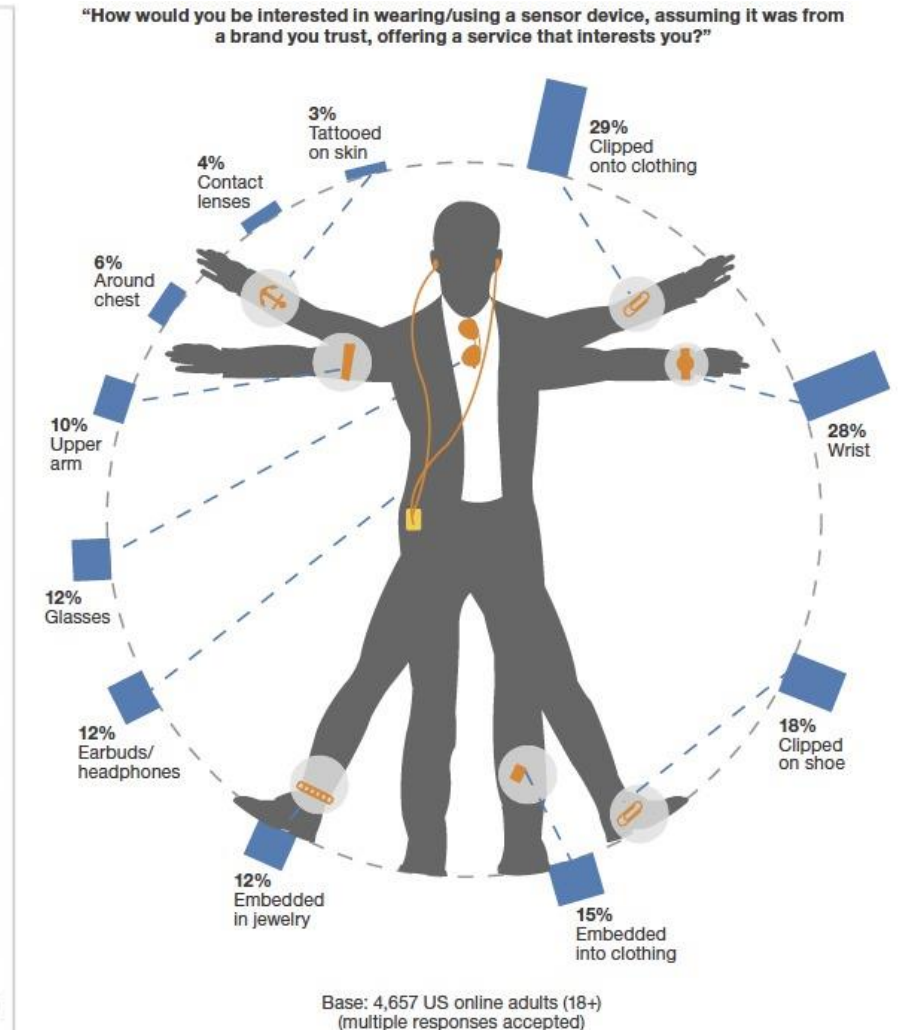
- ▶ Motivation / Applications
- ▶ Process Technology
- ▶ ADC architectures
- ▶ Integration
- ▶ Signal Chain Linearization
- ▶ Conclusion

Motivation / Applications

Application drivers: mobility, pervasive computing, ...

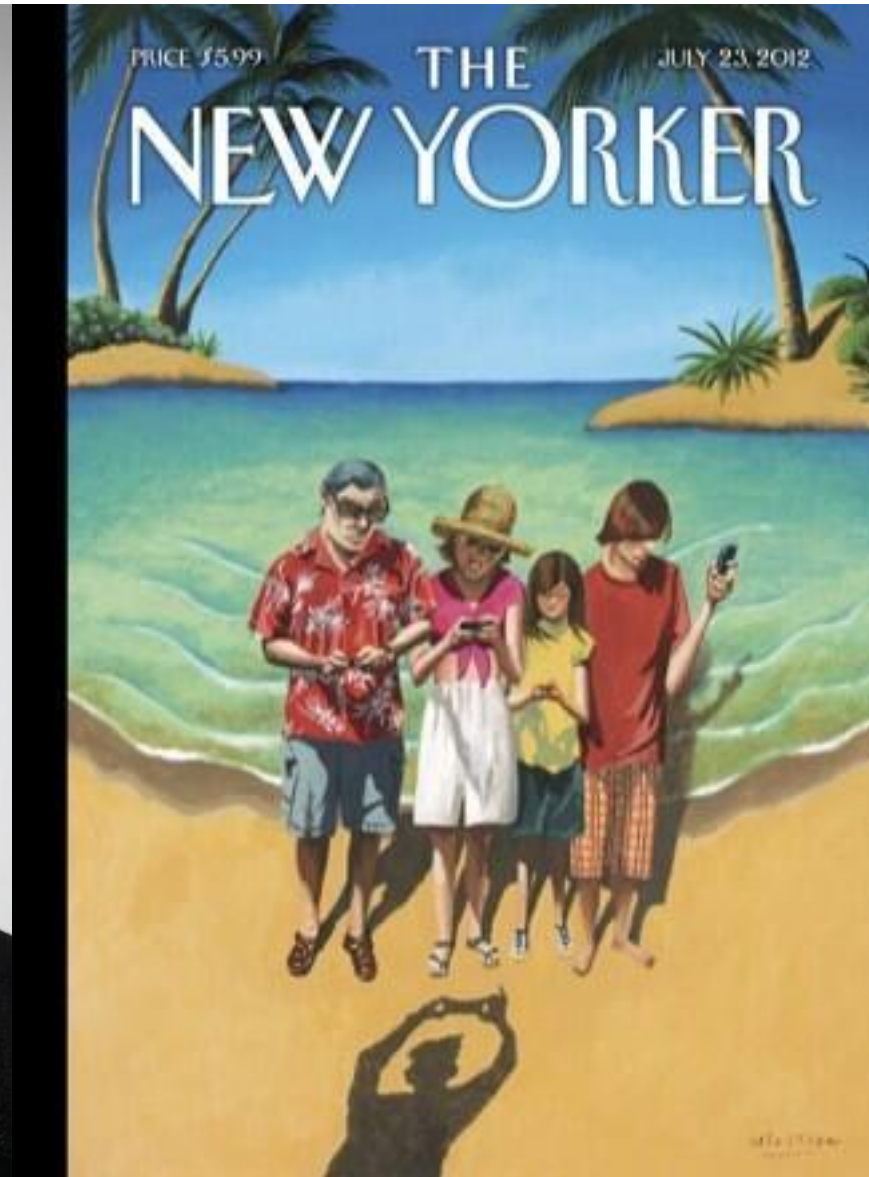


Source: Gartner, IDC, Strategy Analytics, Machina Research, company filings, BII estimates

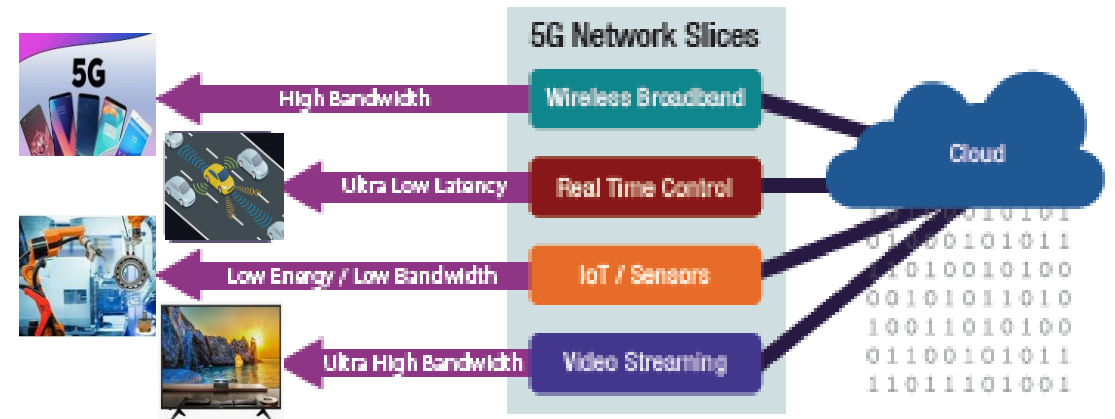
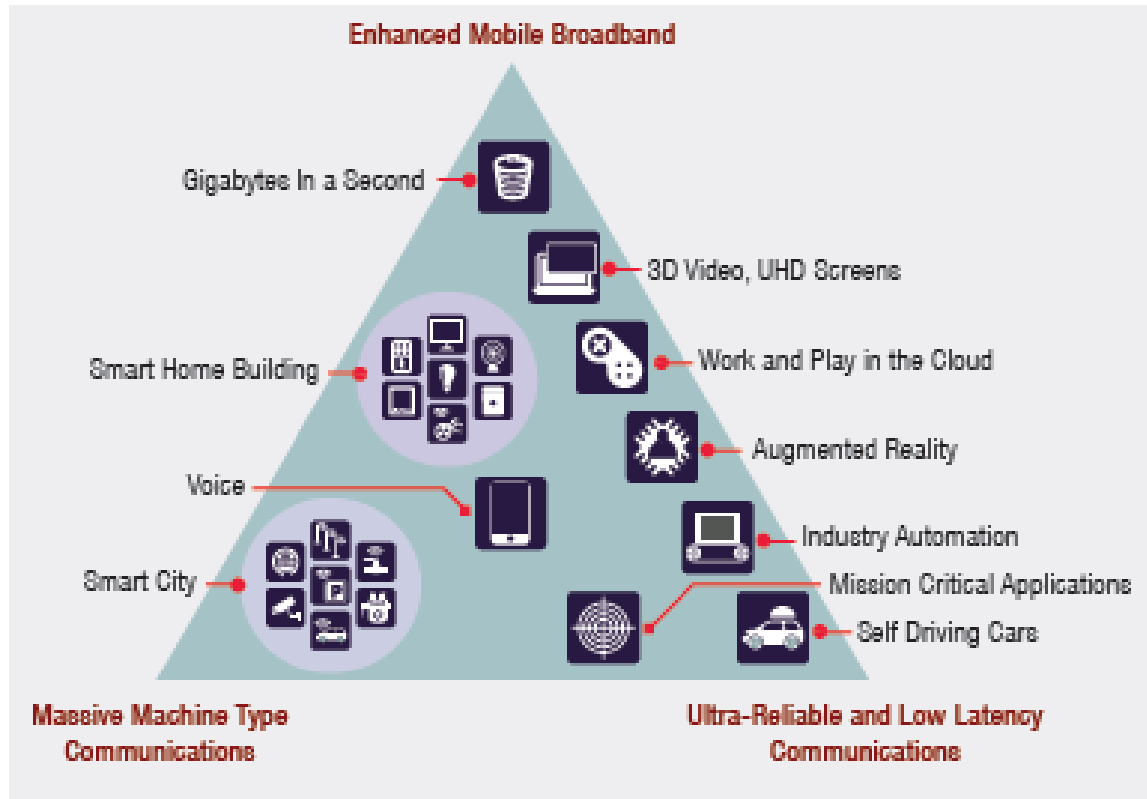


Source: North American Technographics® Consumer Technology Survey, 2013

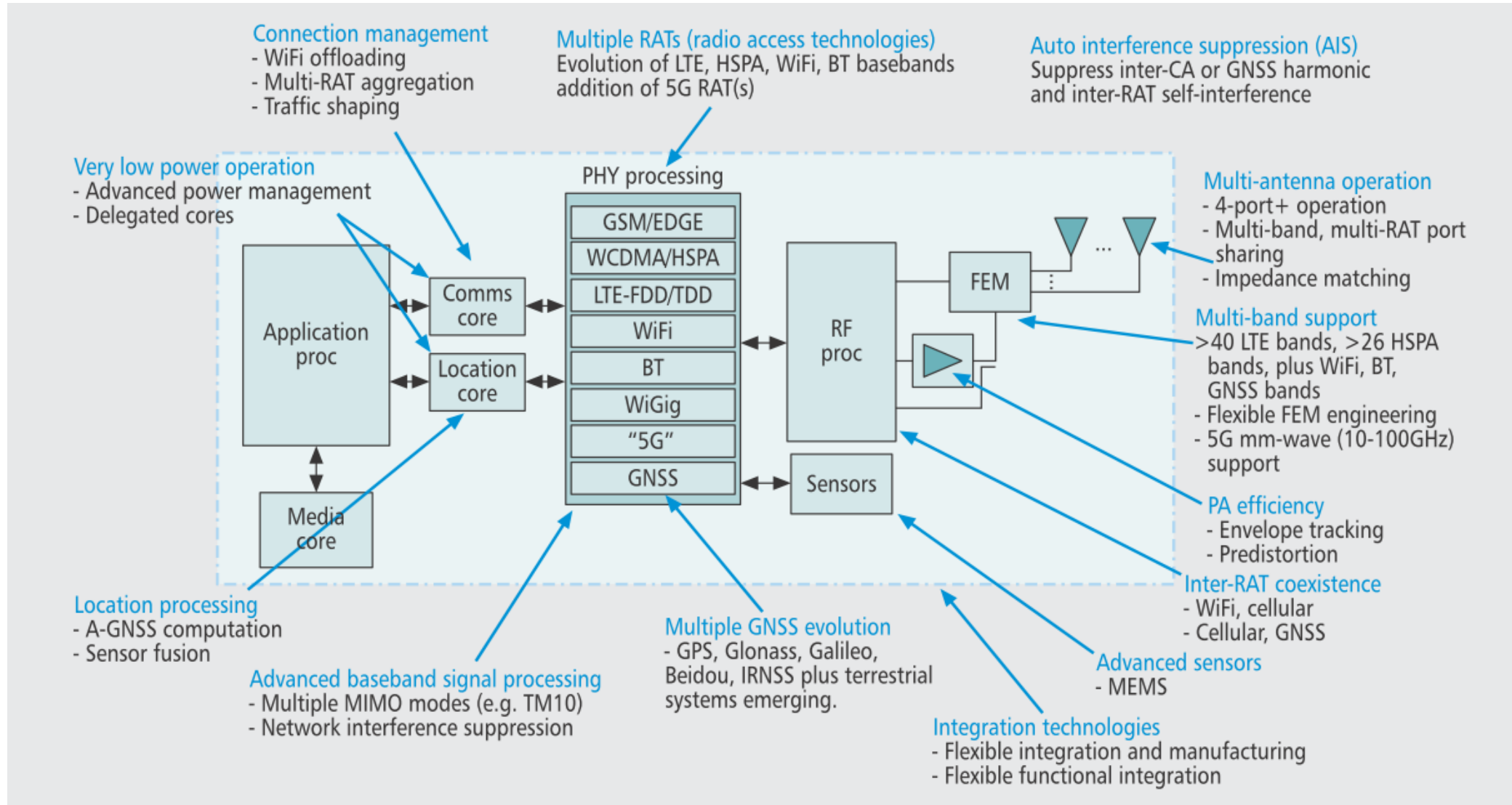
“We wanted flying cars, instead we got 140 characters” – Founders Fund (P. Thiel)



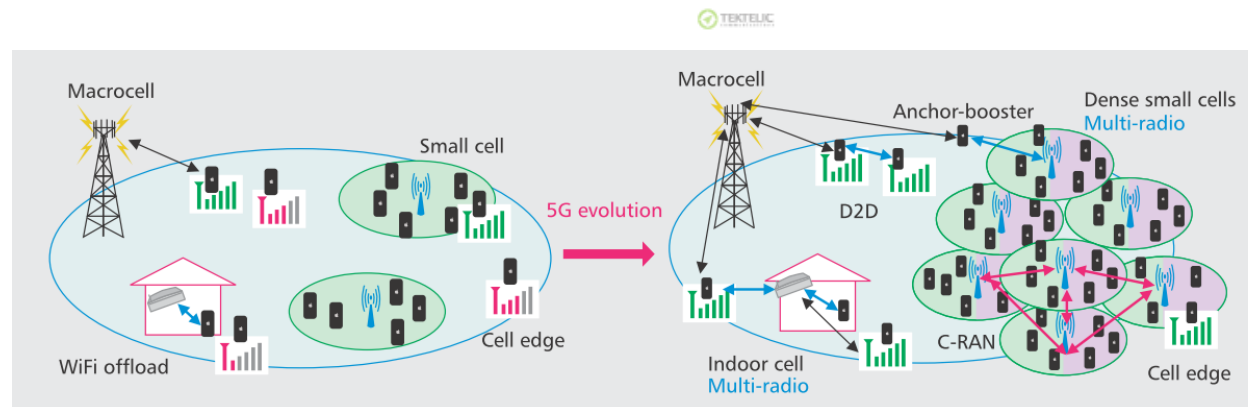
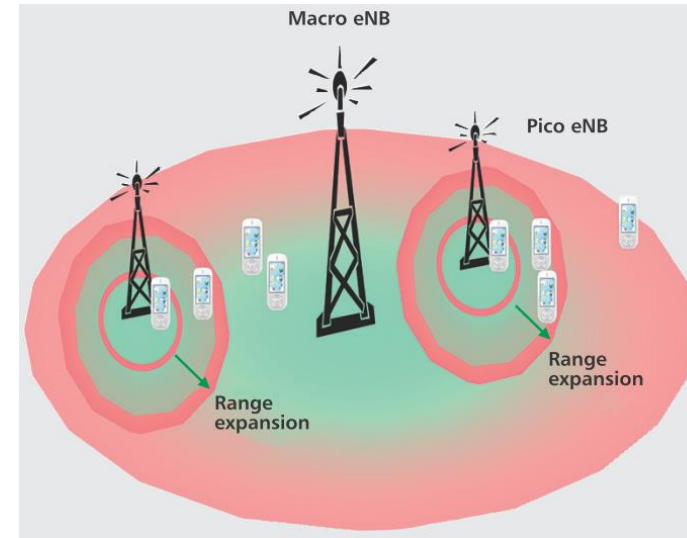
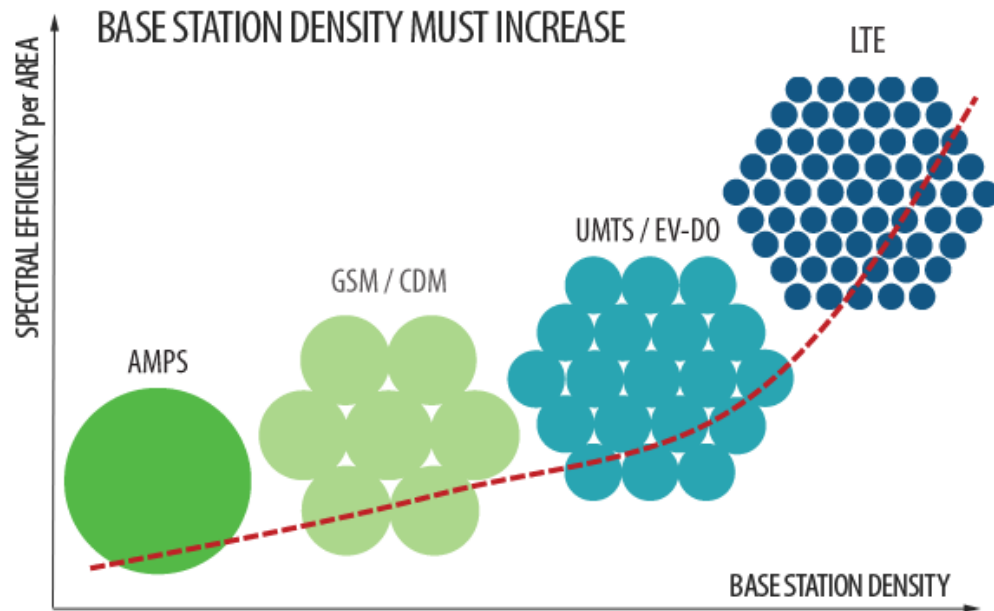
Wireless communication: 5G



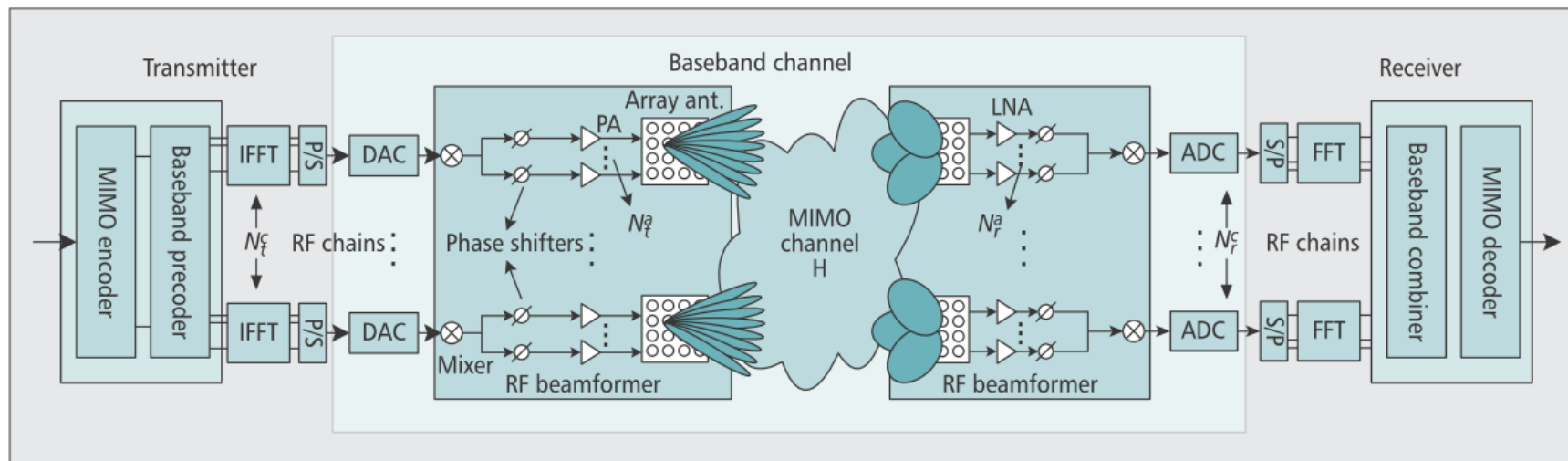
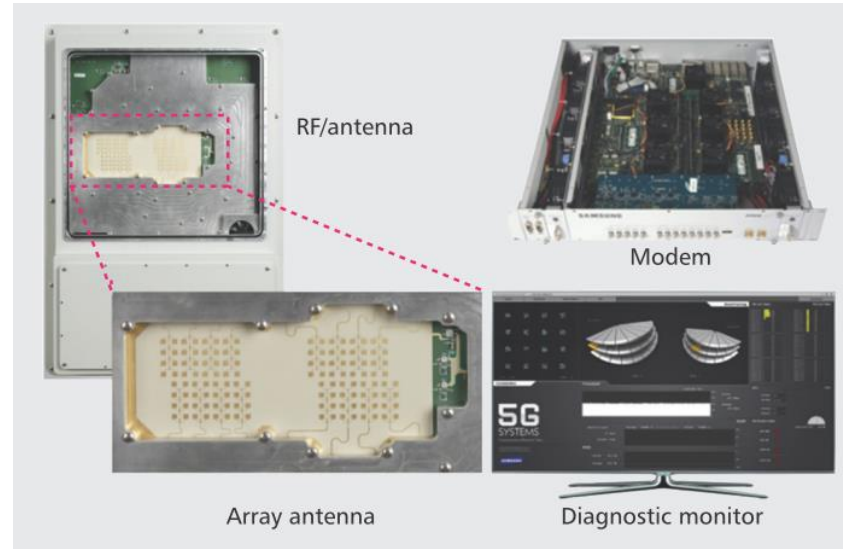
Wireless communication: 5G



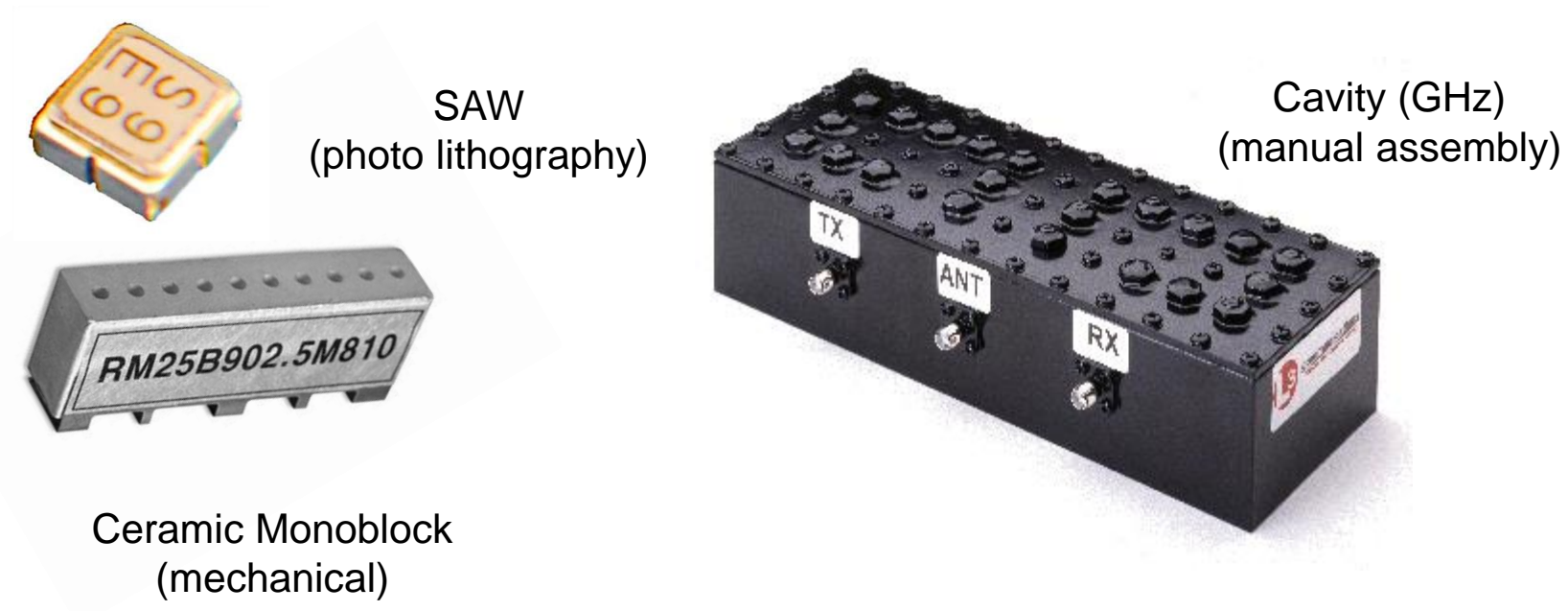
Densification/Range Extension



Massive MIMO / Beamforming



The \$\$ stuff that does not want to scale: duplexer & other filters

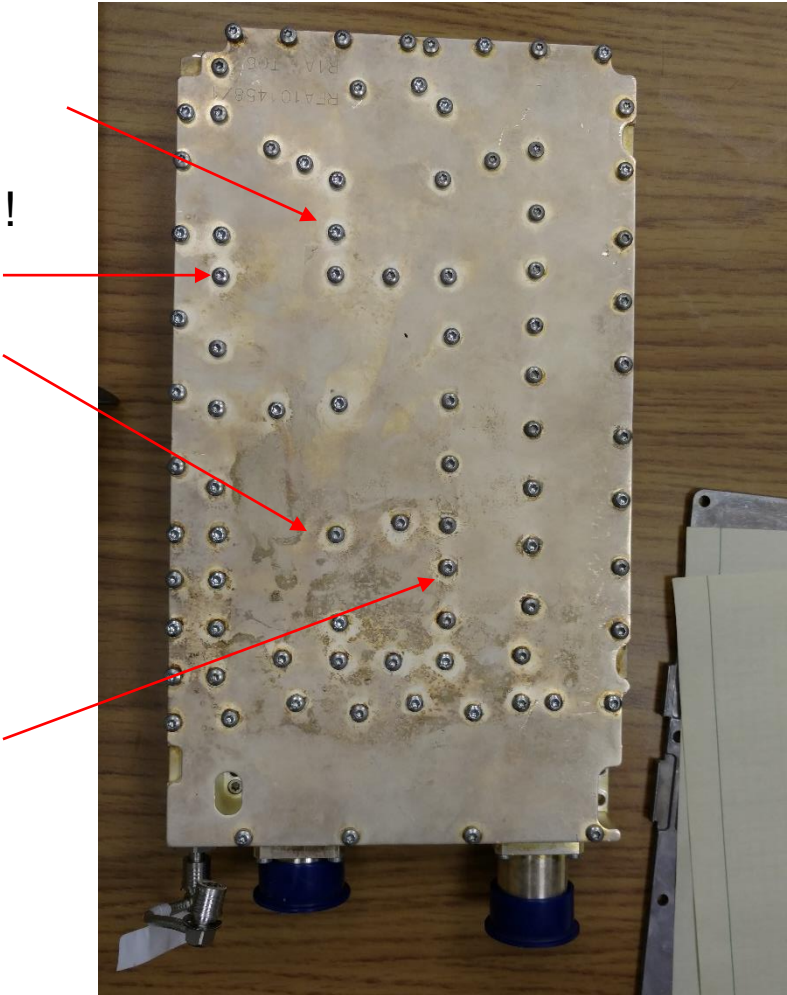


$$\text{size} \propto \text{performance} \quad \text{size} \propto \frac{1}{\text{frequency}}$$

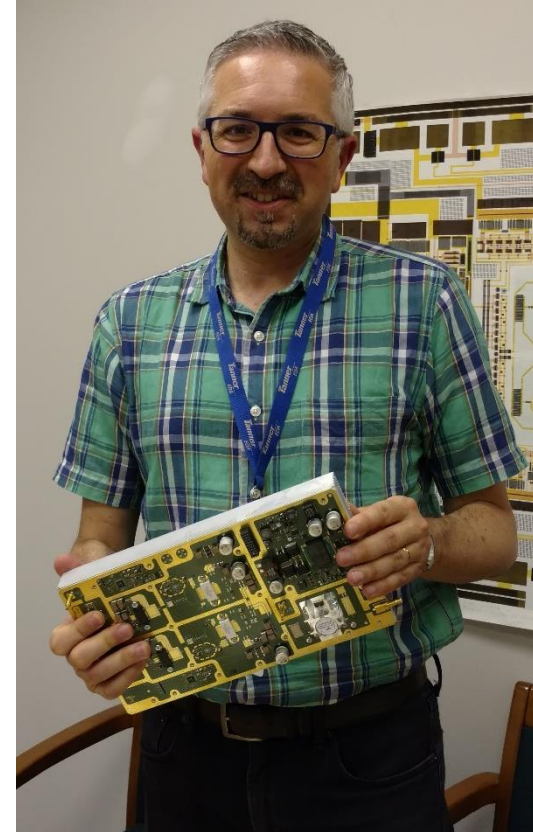
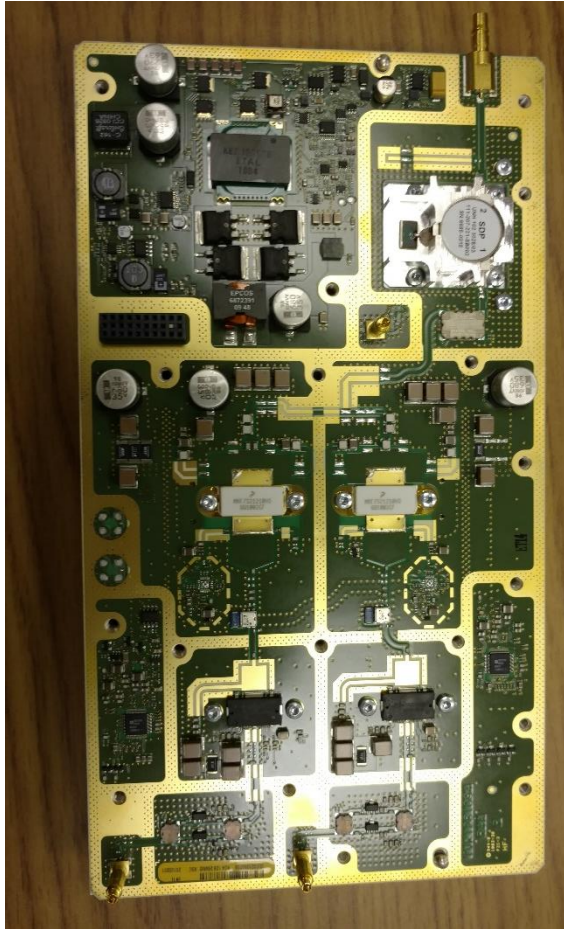
$$\text{cost} \propto \text{size}$$

An actual BTS's duplexer

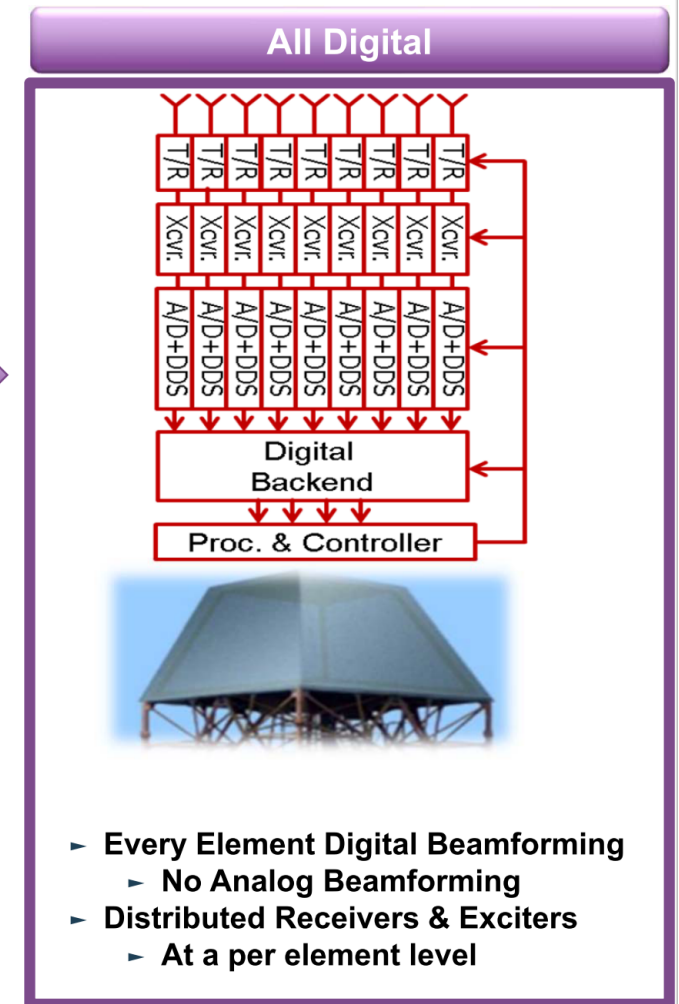
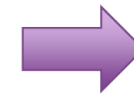
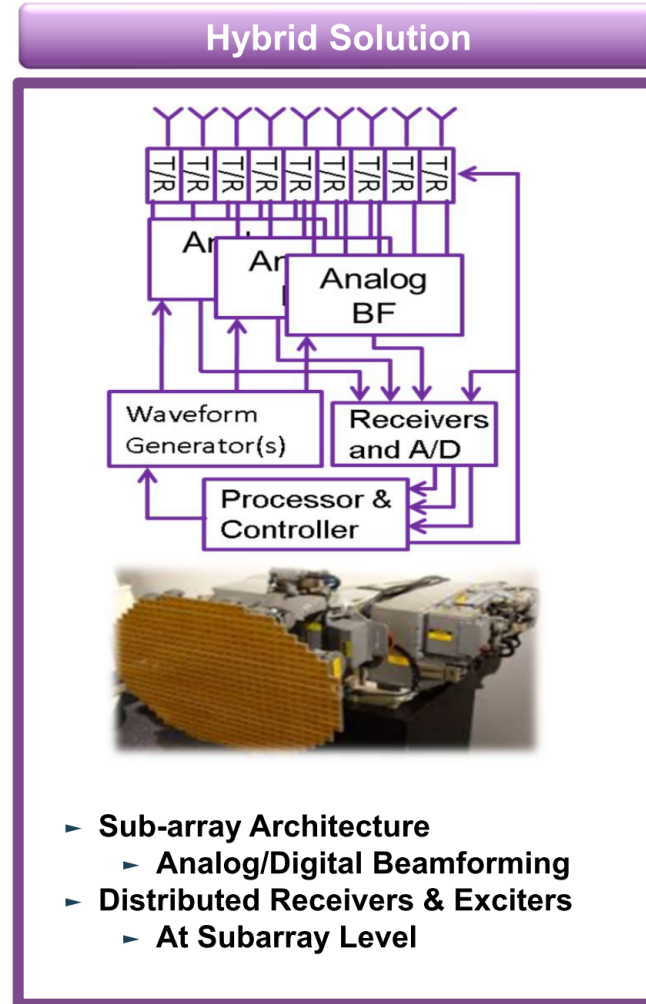
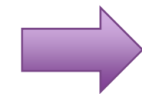
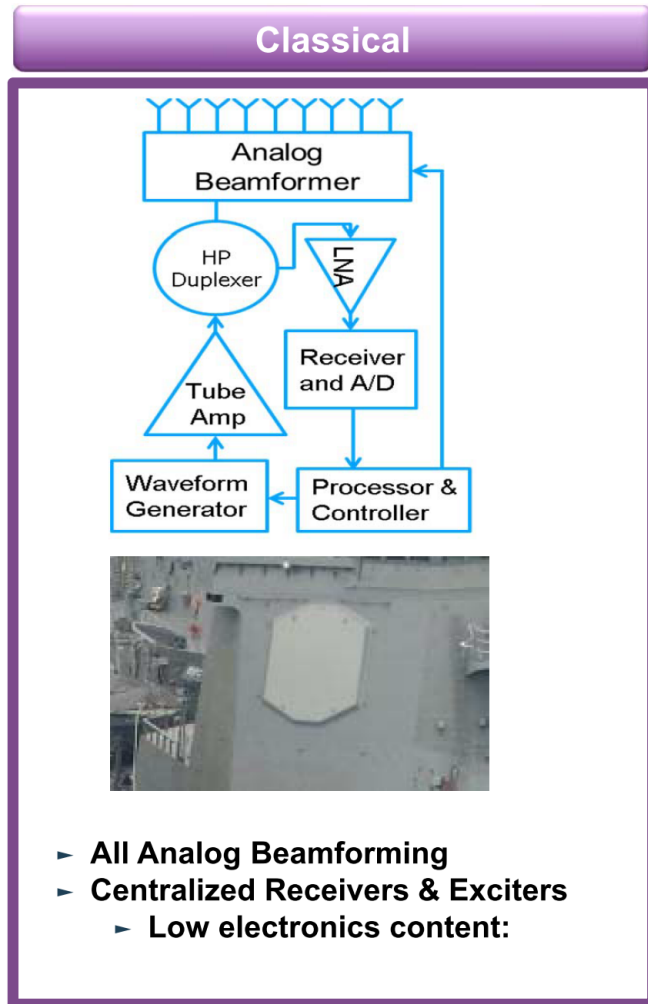
Tuning
screws!!!



An actual power amplifier



Phased array system evolution

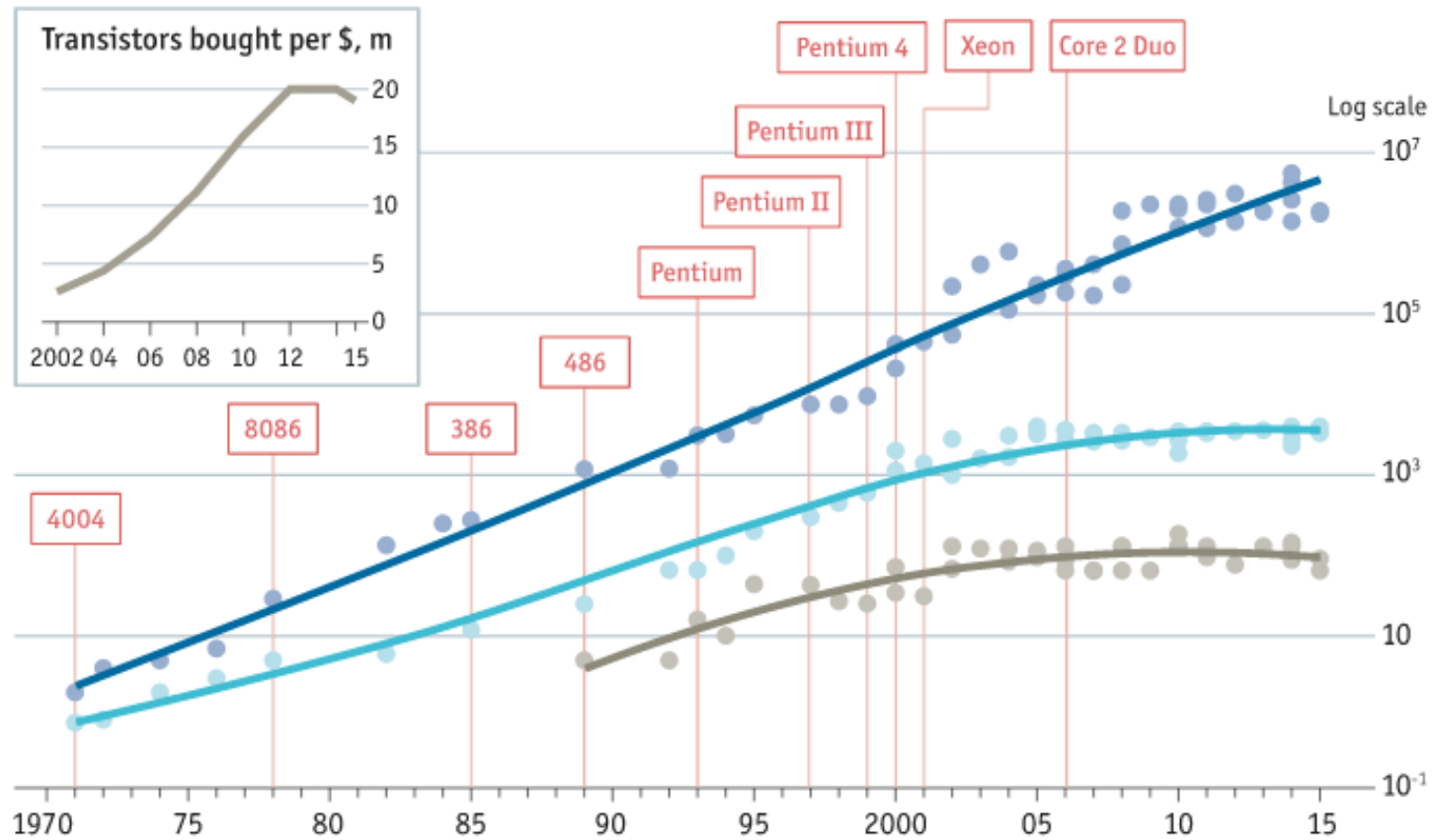


Process Technology

Moore's law

Stuttering

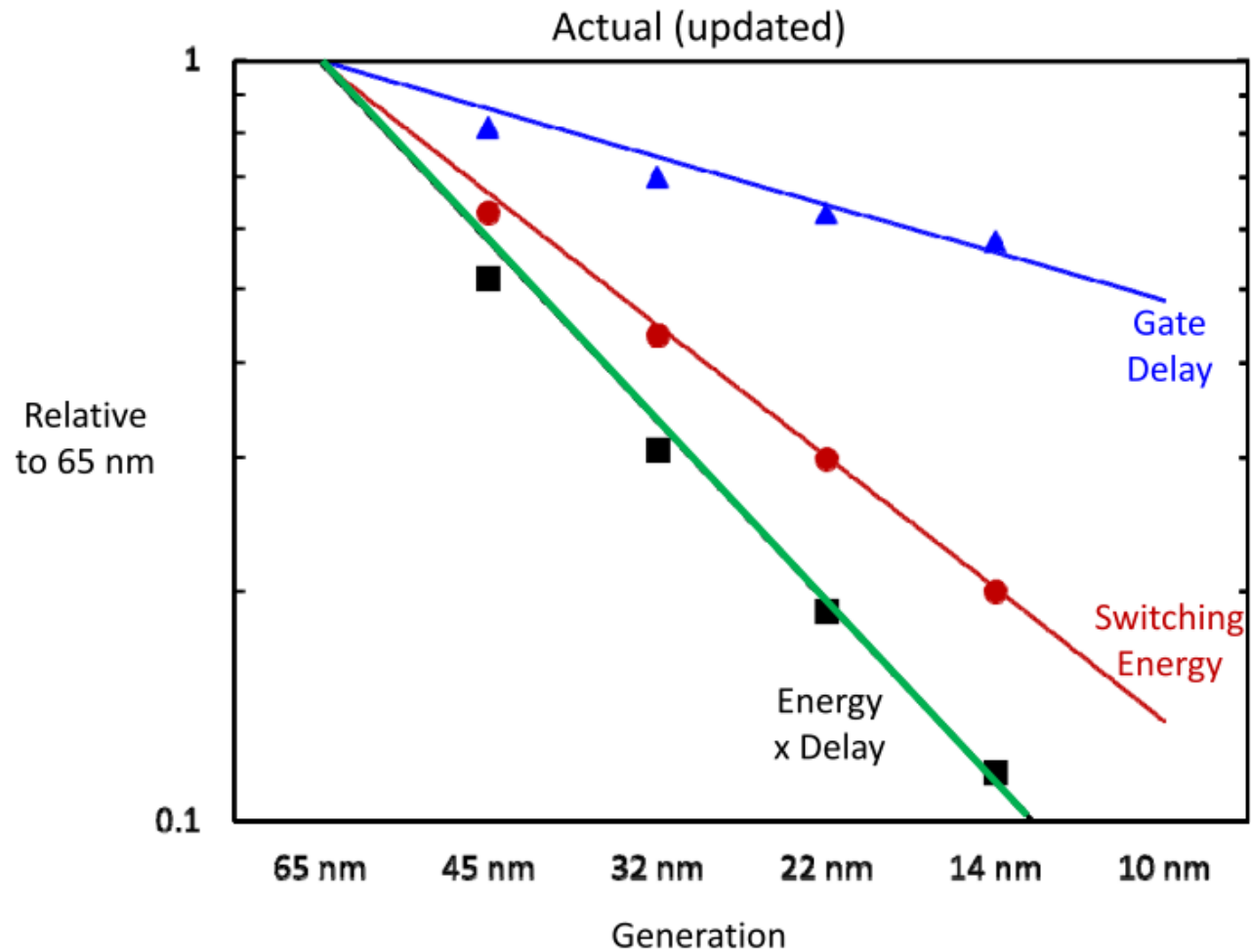
● Transistors per chip, '000 ● Clock speed (max), MHz ● Thermal design power*, w □ Chip introduction dates, selected



Sources: Intel; press reports; Bob Colwell; Linley Group; IB Consulting; *The Economist*

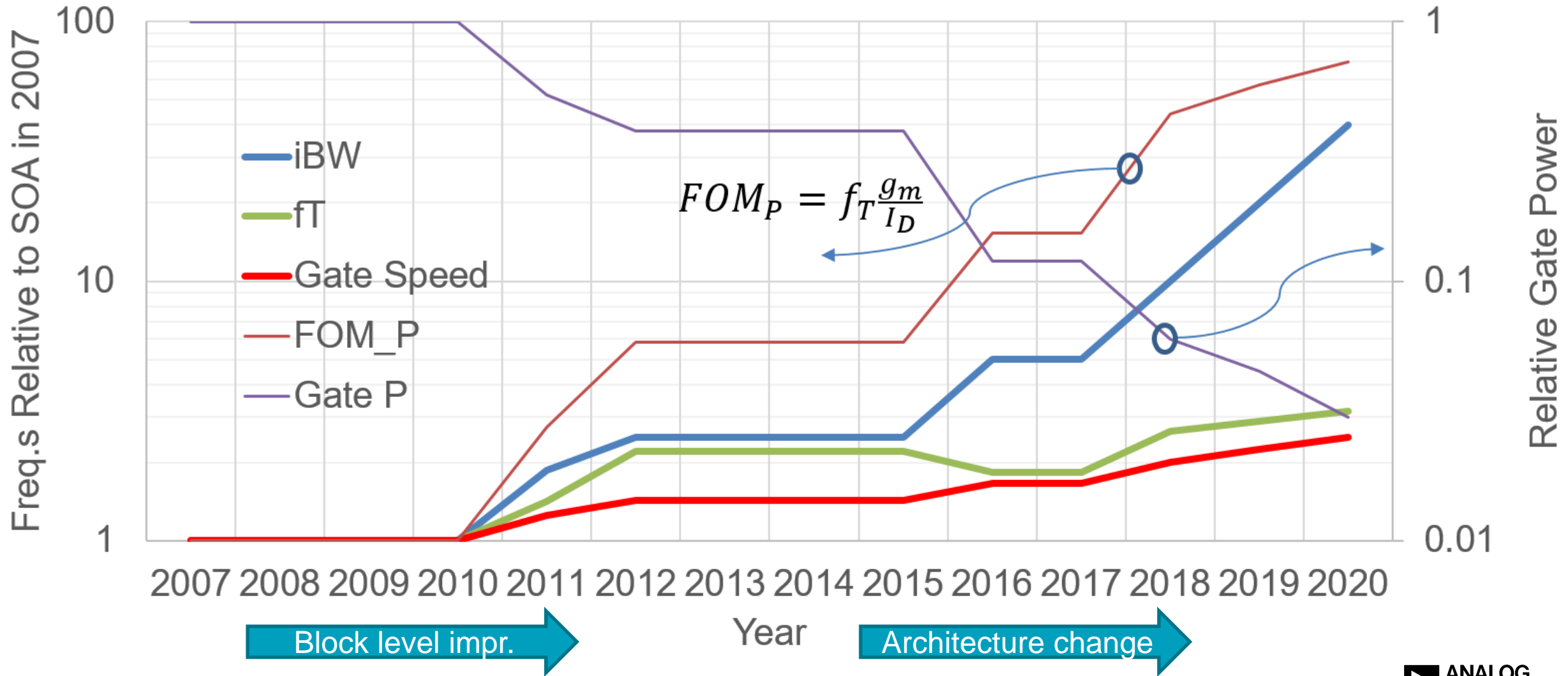
*Maximum safe power consumption

Higher digital power efficiency, but not (much) higher device speed!



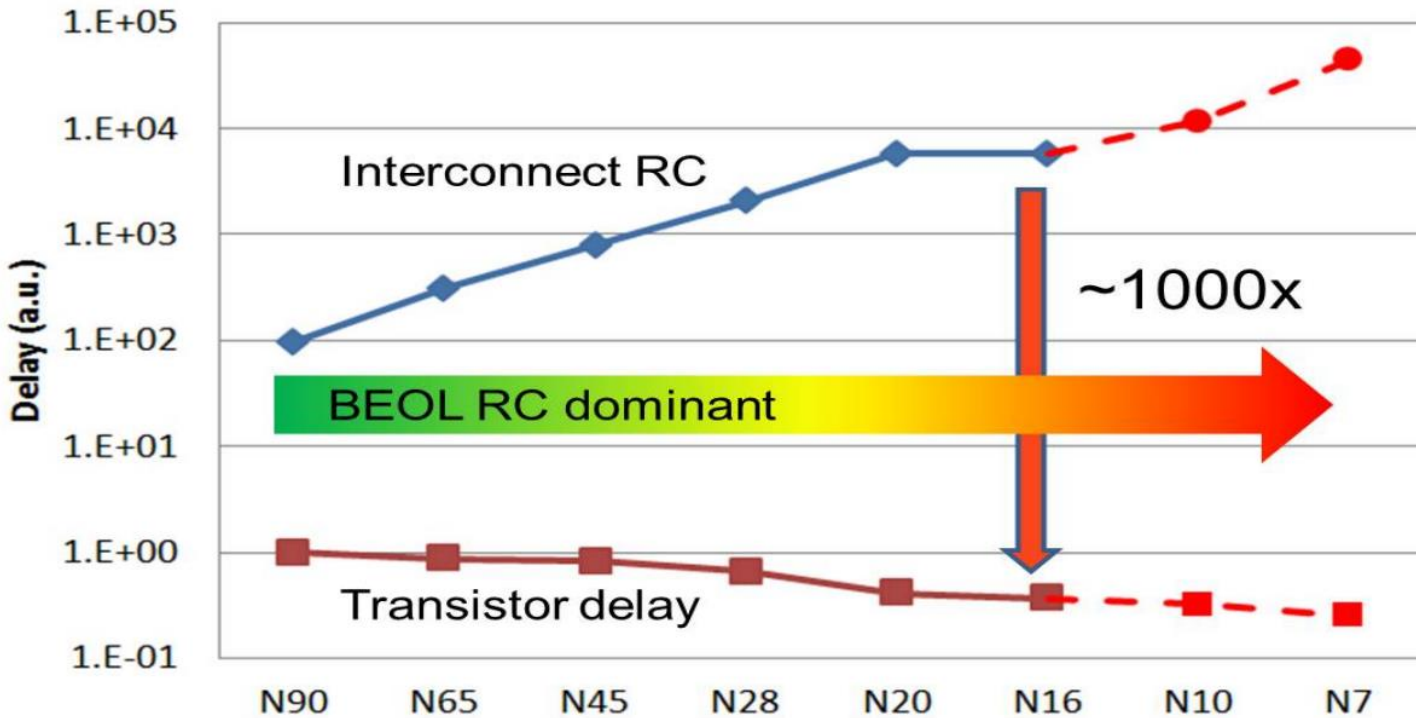
Source: W.M.Holt, “Moore’s Law: A path going forward”, ISSCC 2016

Application pull: Wireless Infrastructure (BTS) bandwidth demand versus MS CMOS capability

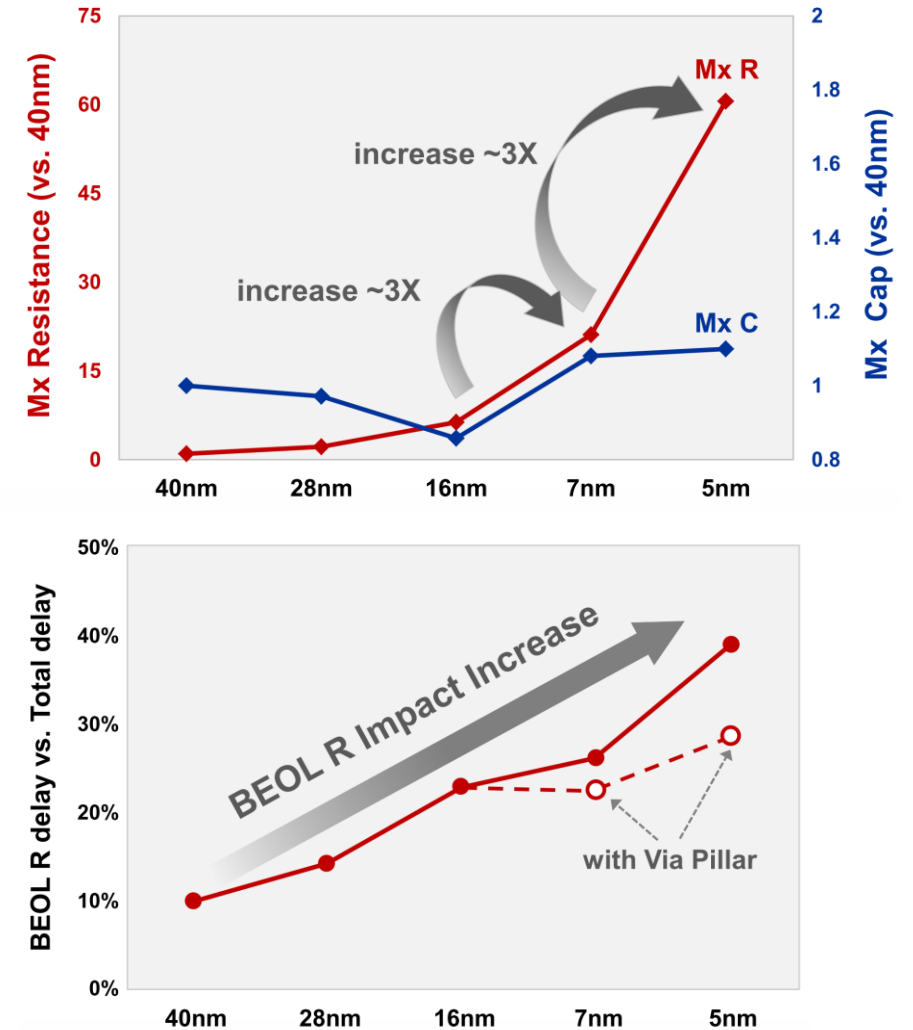


G. Manganaro, "Emerging data converter architectures and techniques," IEEE CICC, 2018.

Die interconnects are the biggest bottleneck



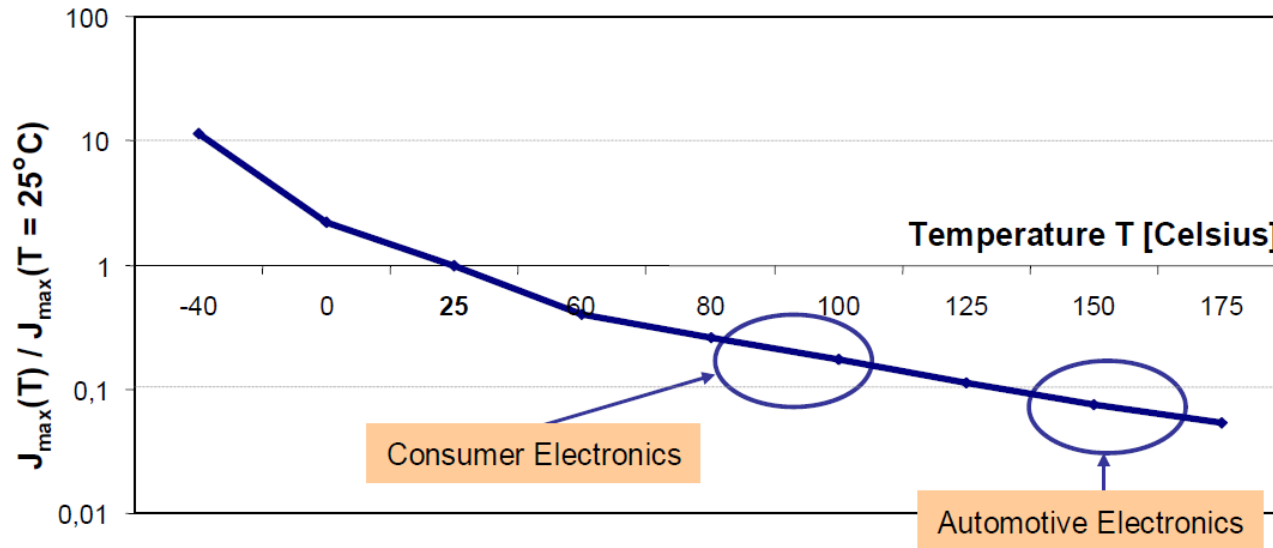
Source: G. Yeap (Qualcomm), IEEE Electron Devices Meeting (IEDM), 2013



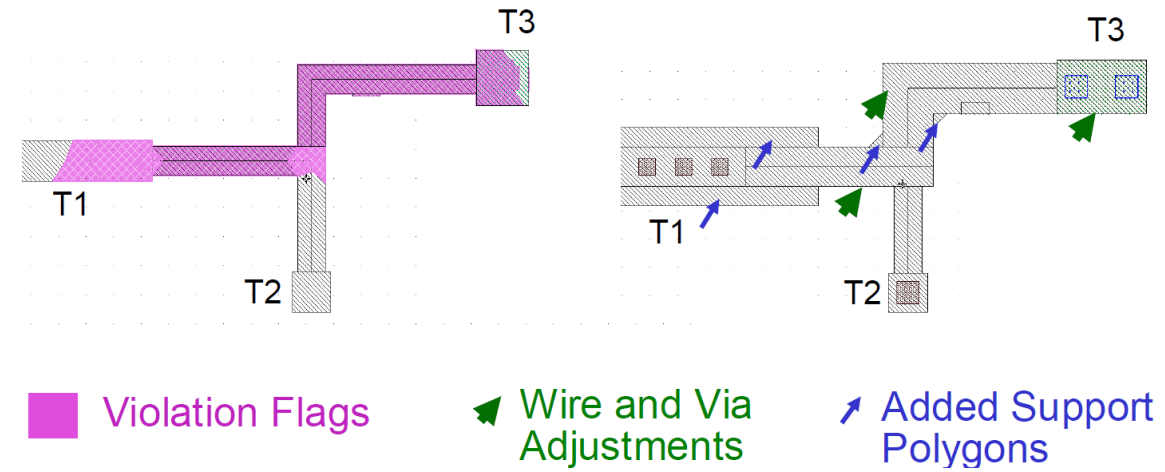
C. Hou (TSMC), ISSCC 2017 & L. Lu (TSMC), ISPD 2017

Electromigration

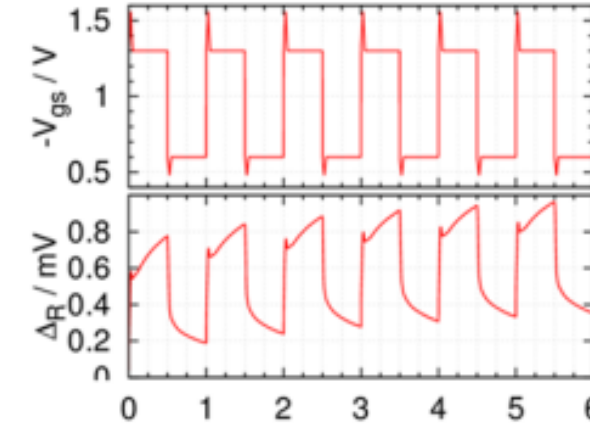
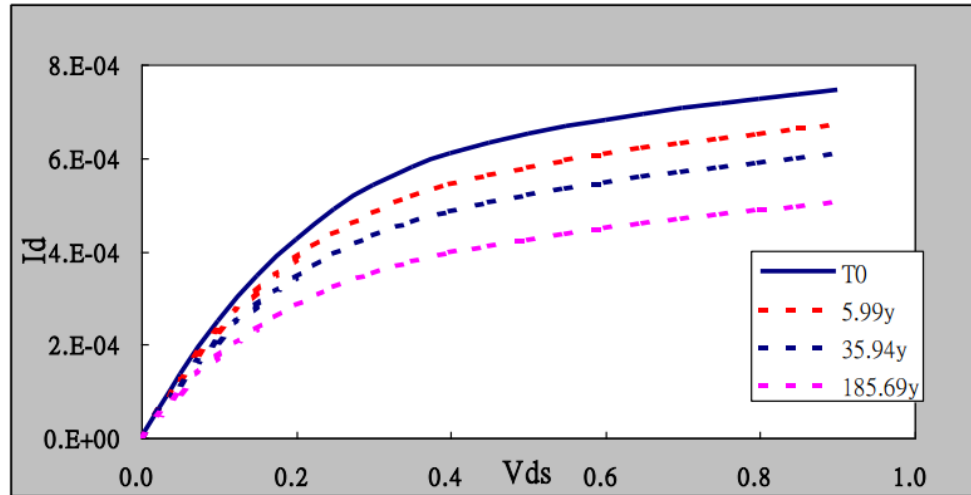
$J_{\max}(T)$ compared to $J_{\max}(T_{\text{ref}} = 25^{\circ}\text{C})$ [1]



The maximum permissible current density of an aluminum metallization, calculated at e.g. 25°C, is reduced significantly when the temperature of the interconnect rises



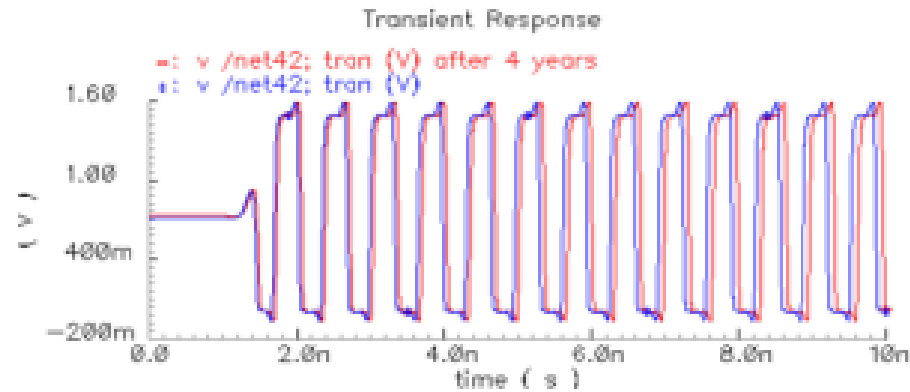
Device Aging



V_t shift due to NBTI degradation

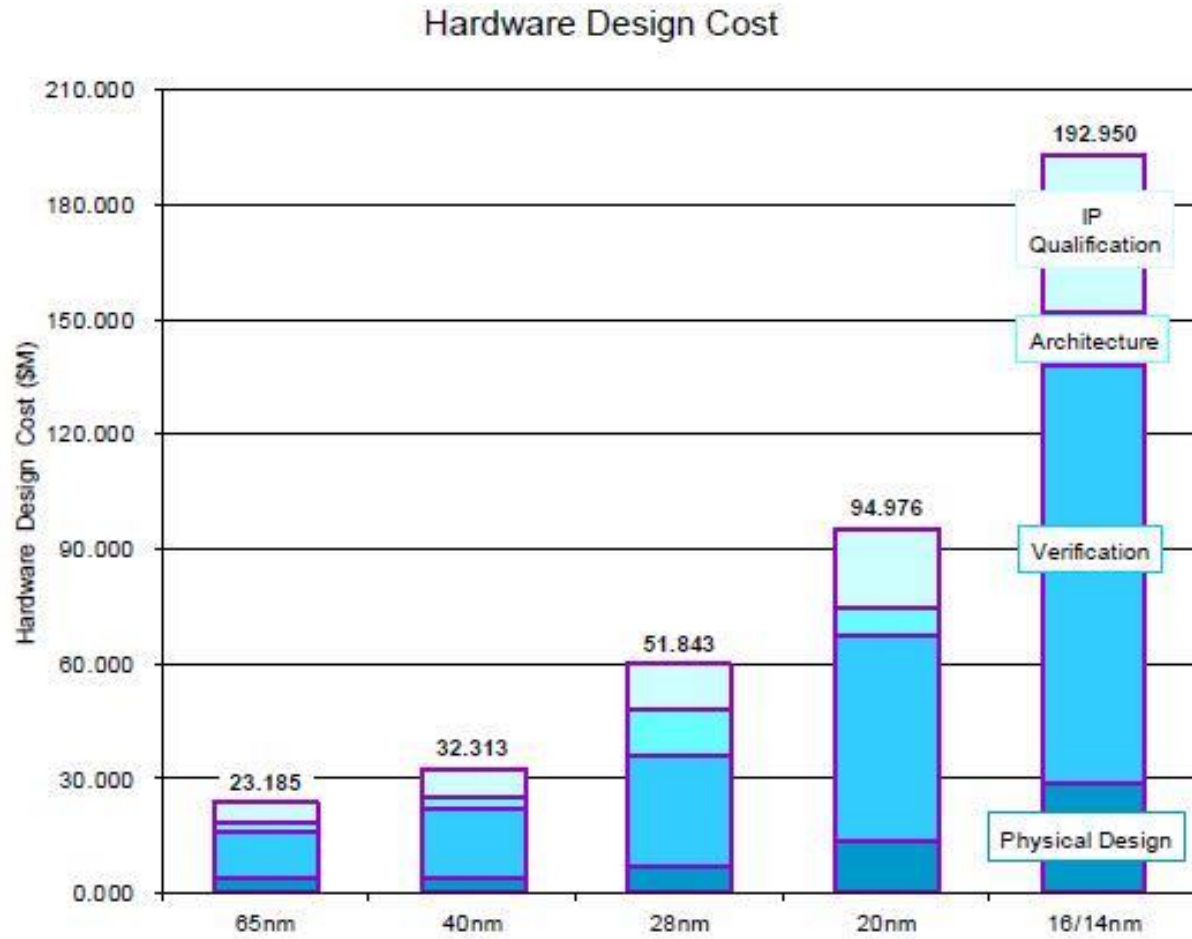
Run	Test	Output	Nominal	Spec	Meas
fresh	for_dut_20140428:r0c_Pipe1st_0TA_TB:1	vout_c12			
fresh	for_dut_20140428:r0c_Pipe1st_0TA_TB:1	/V25/MINUS			
fresh	for_dut_20140428:r0c_Pipe1st_0TA_TB:1	/ICL/V32R			
fresh	for_dut_20140428:r0c_Pipe1st_0TA_TB:1	Voffset	68.91u	range -3u 3u	
stress	for_dut_20140428:r0c_Pipe1st_0TA_TB:1	vout_c12			
stress	for_dut_20140428:r0c_Pipe1st_0TA_TB:1	/V25/MINUS			
stress	for_dut_20140428:r0c_Pipe1st_0TA_TB:1	/ICL/V32R			
stress	for_dut_20140428:r0c_Pipe1st_0TA_TB:1	Voffset	68.91u	range -3u 3u	
10 yr	for_dut_20140428:r0c_Pipe1st_0TA_TB:1	vout_c12			
10 yr	for_dut_20140428:r0c_Pipe1st_0TA_TB:1	/V25/MINUS			
10 yr	for_dut_20140428:r0c_Pipe1st_0TA_TB:1	/ICL/V32R			
10 yr	for_dut_20140428:r0c_Pipe1st_0TA_TB:1	Voffset	-115.6u	range -3u 3u	

Offset voltage violated after 10 years



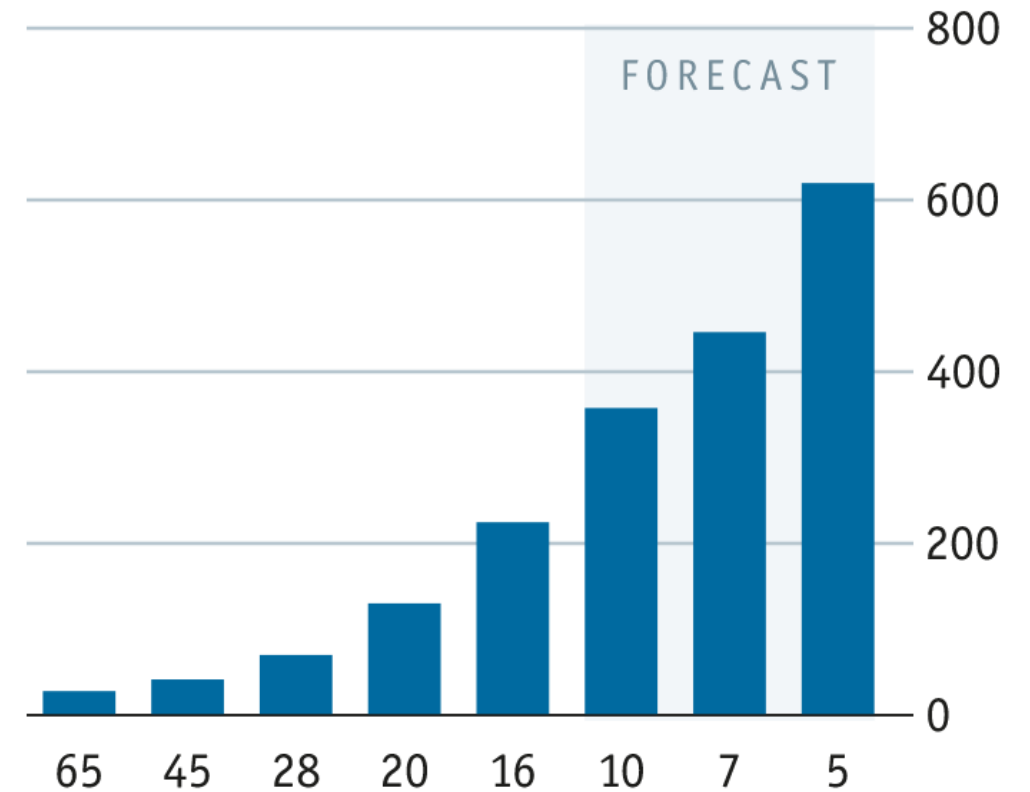
Frequency shift after 4 years of op.

Complexity drives development cost



Source: International Business Strategies, Inc 2013 report

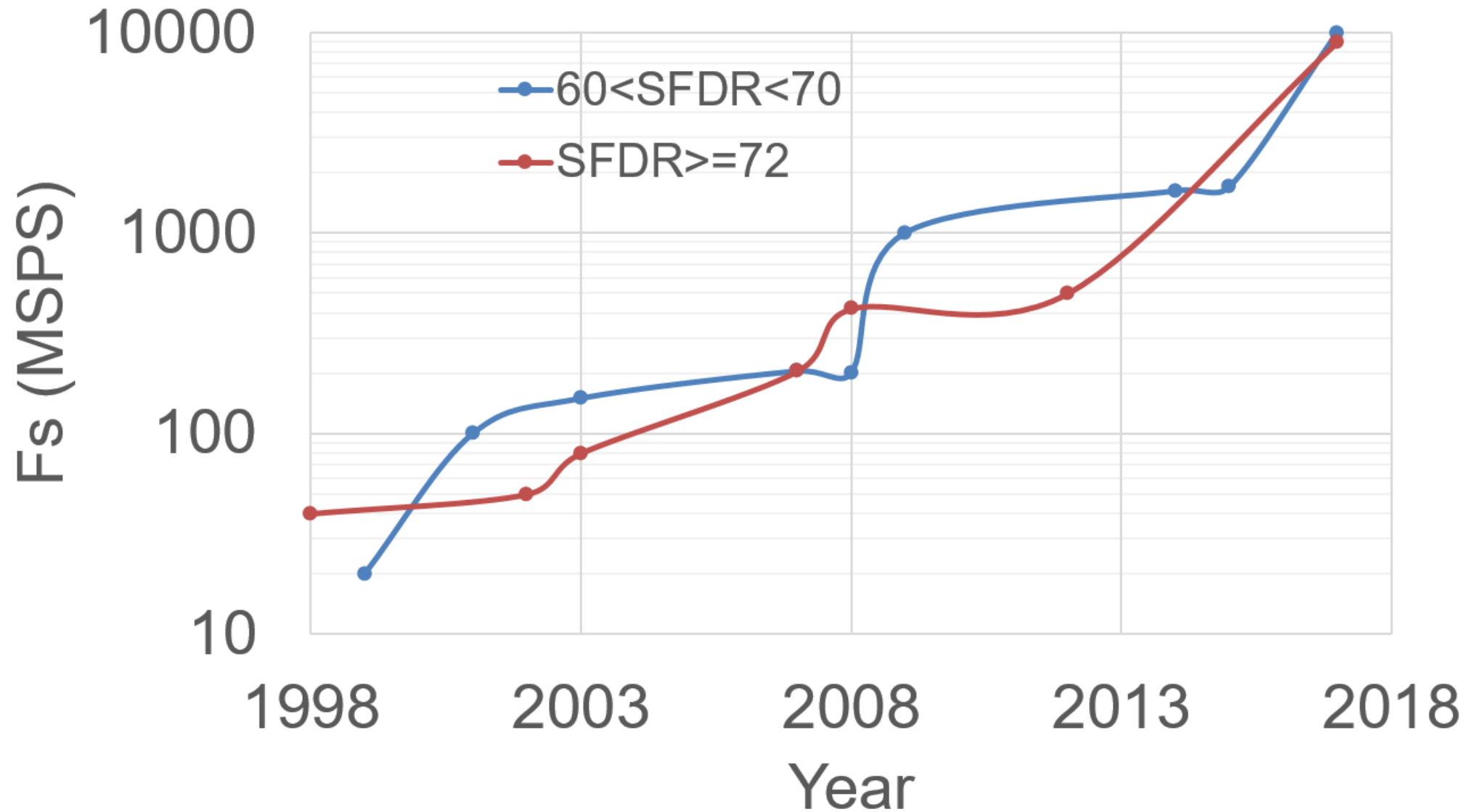
Design cost by chip component size in nm, \$m



Source: IB Consulting

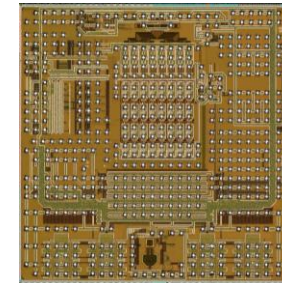
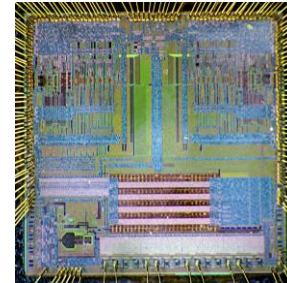
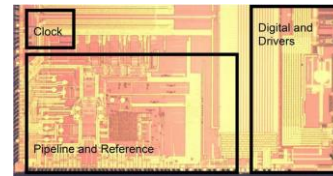
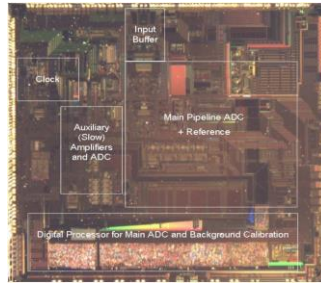
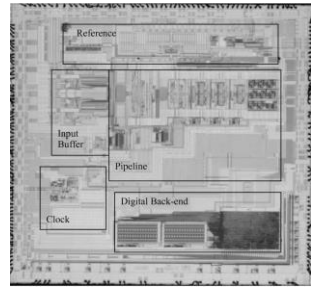
ADC architectures

Technology progression: 12b/14b High Speed (HS) ADC progression



G. Manganaro, "Emerging data converter architectures and techniques," IEEE CICC, 2018.

Analog/Digital composition for HS ADC cores



14b/125MSPS

16b/250MSPS

14b/1.25GSPS

14b/3GSPS

12b/10GSPS

0.35u BiCMOS

0.18u BiCMOS

65nm CMOS

28nm CMOS

28nm CMOS

85%A/15%D

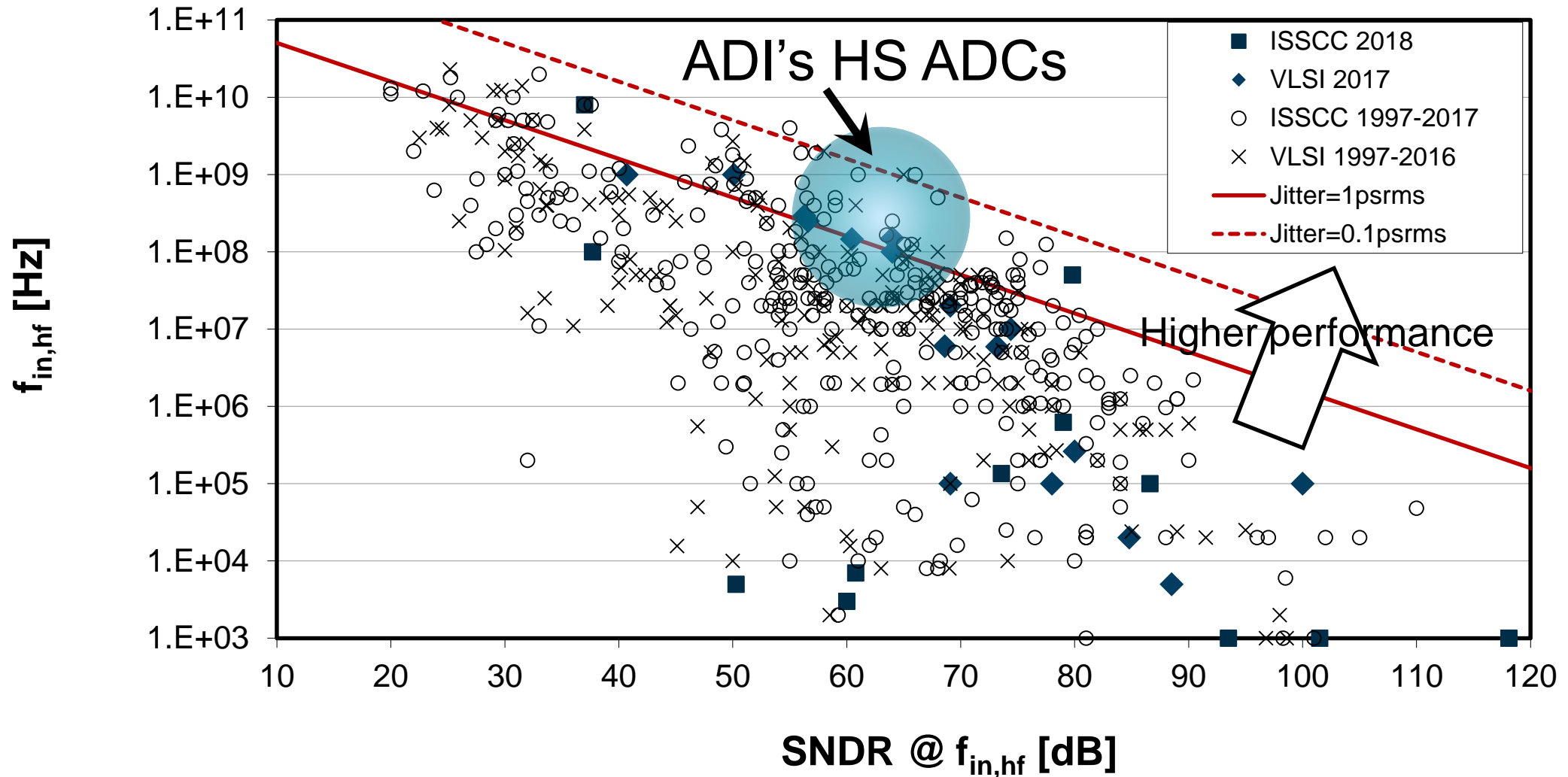
80%A/20%D

75%A/25%D

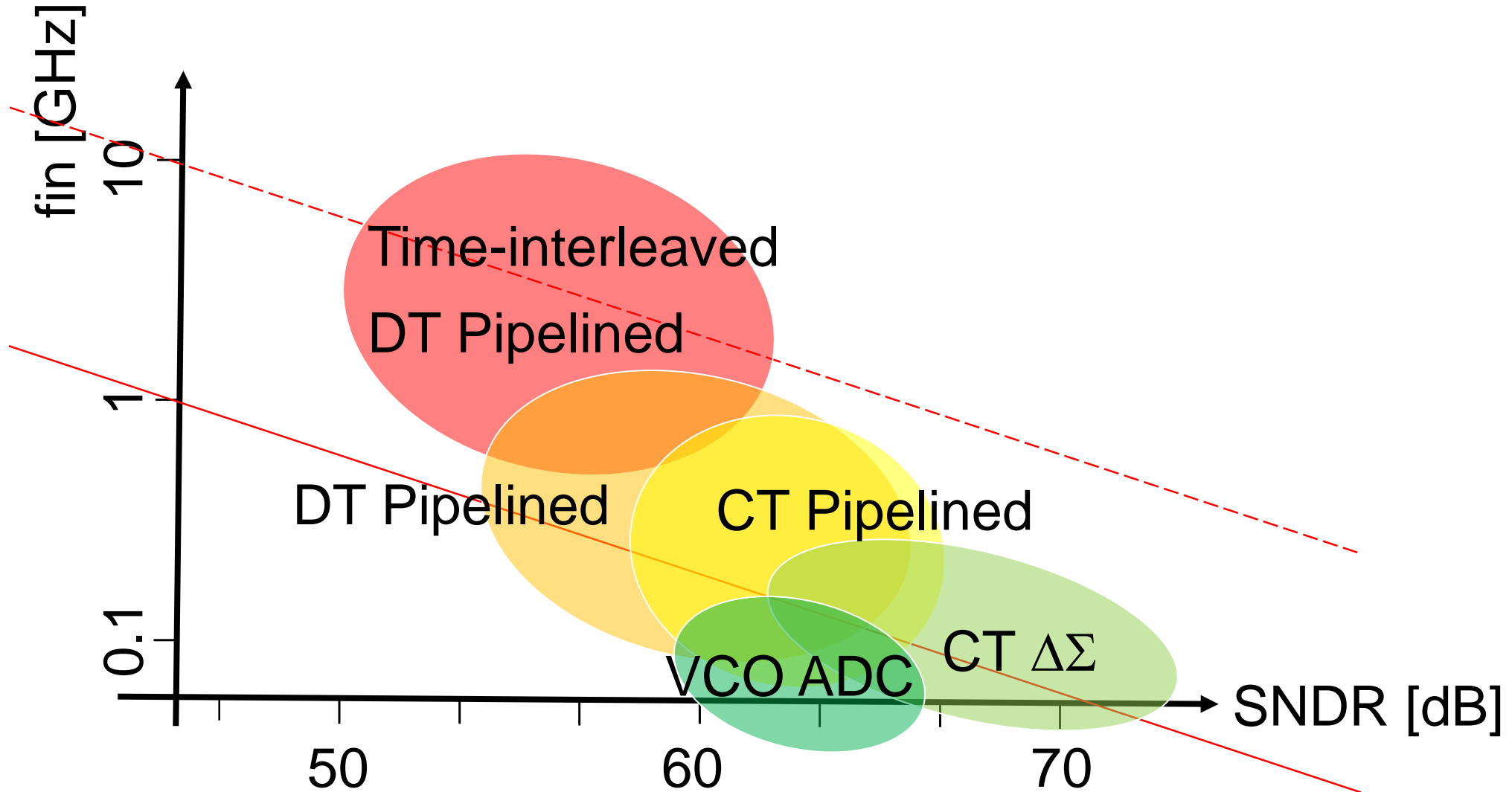
70%A/30%D

60%A/40%D

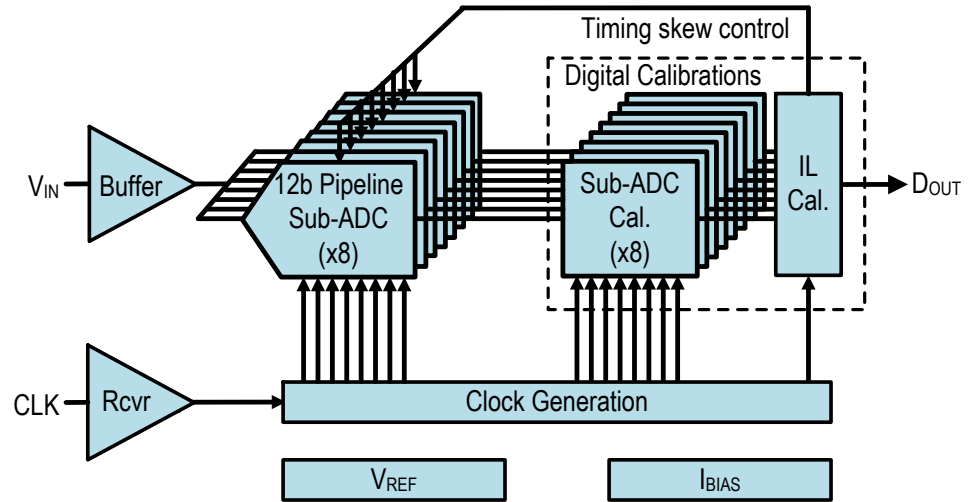
Architectures (no one fits all): ADC “Aperture plot” (i.e. Bandwidth vs. Dyn Range or sample rate vs. resolution)



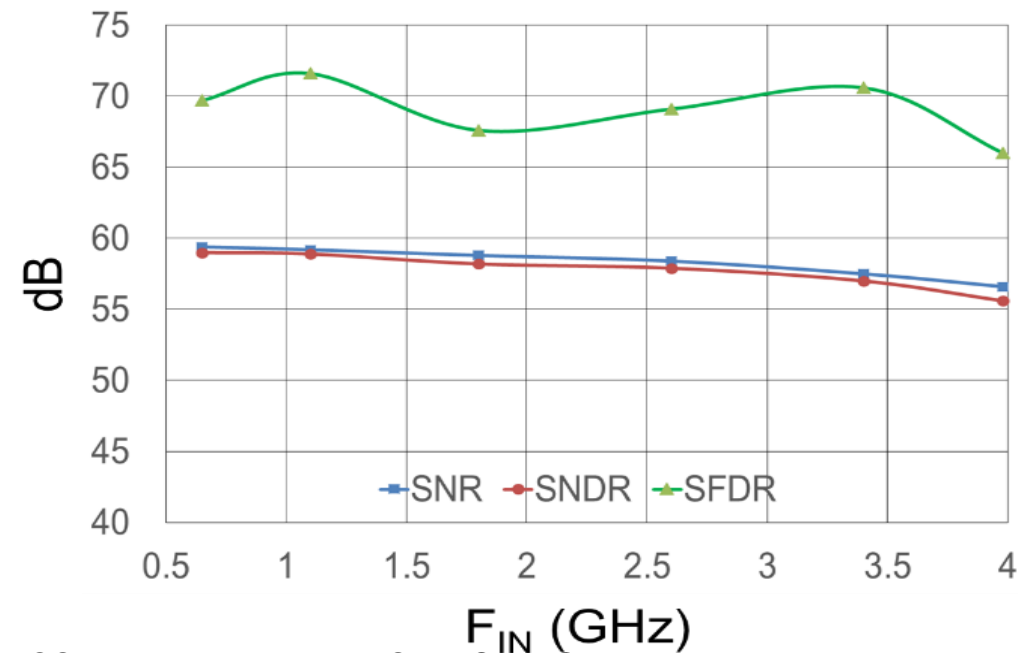
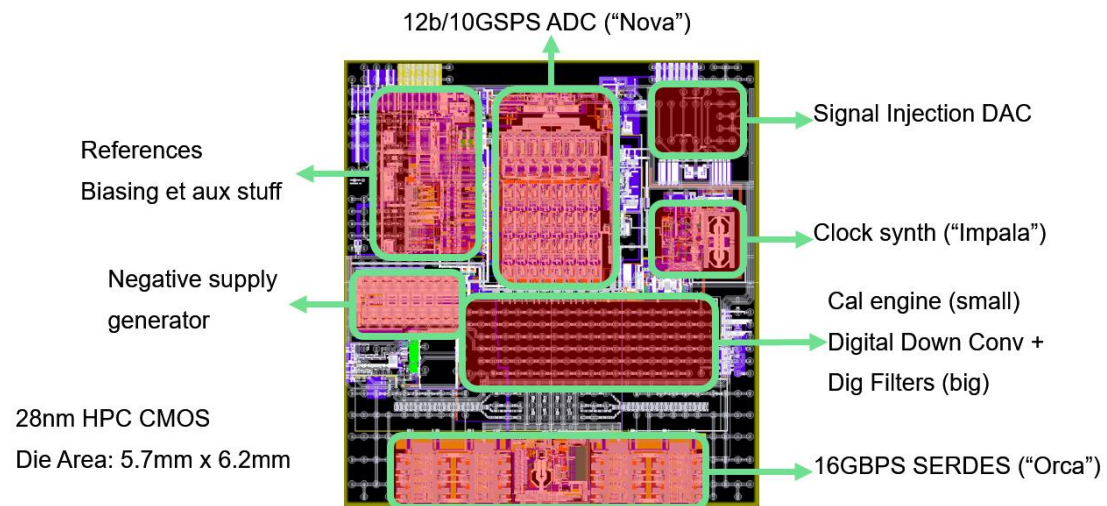
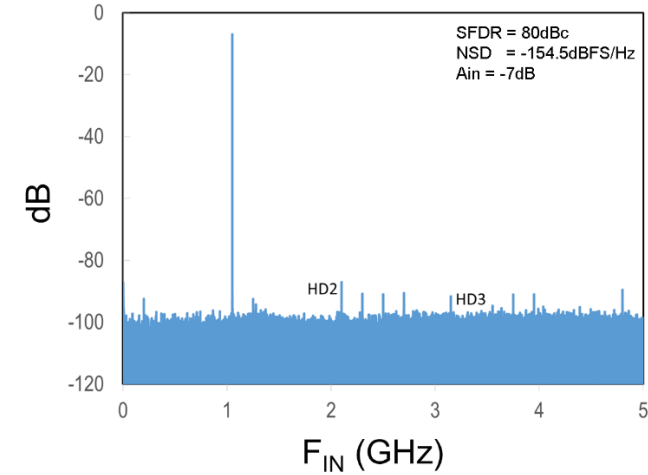
ADI's ADC architectures: one cannot fit all



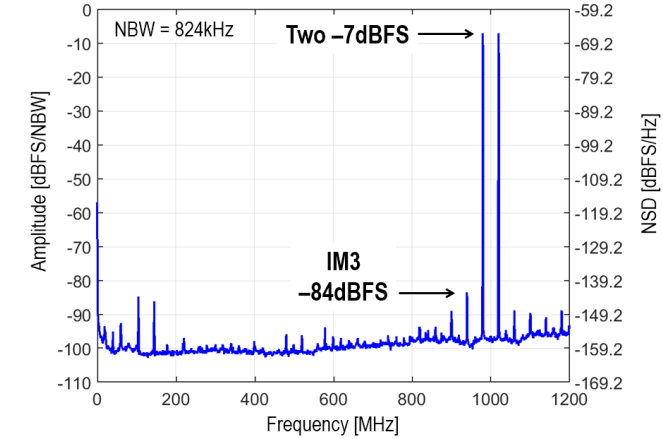
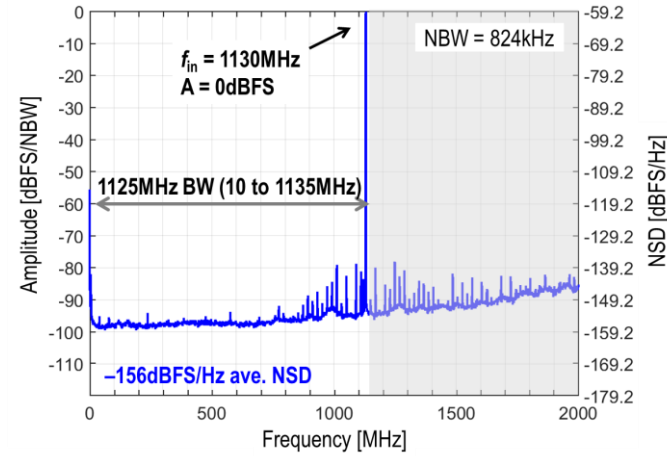
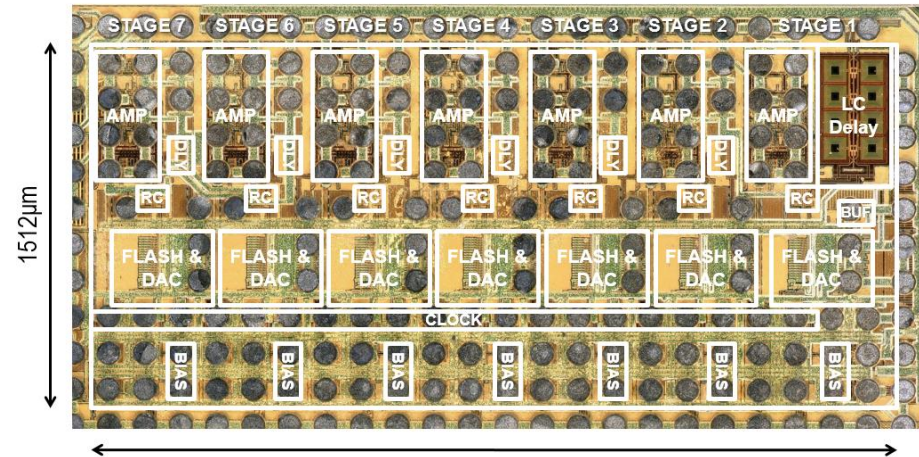
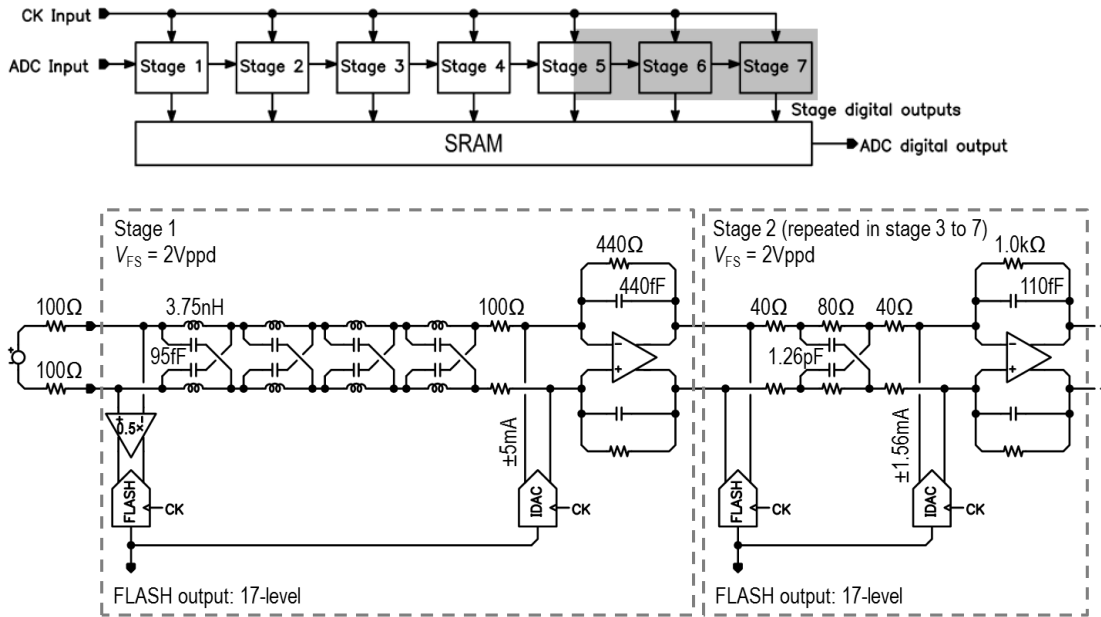
12b/10GSPS ADC: 8x interleaved Analog to Digital converter



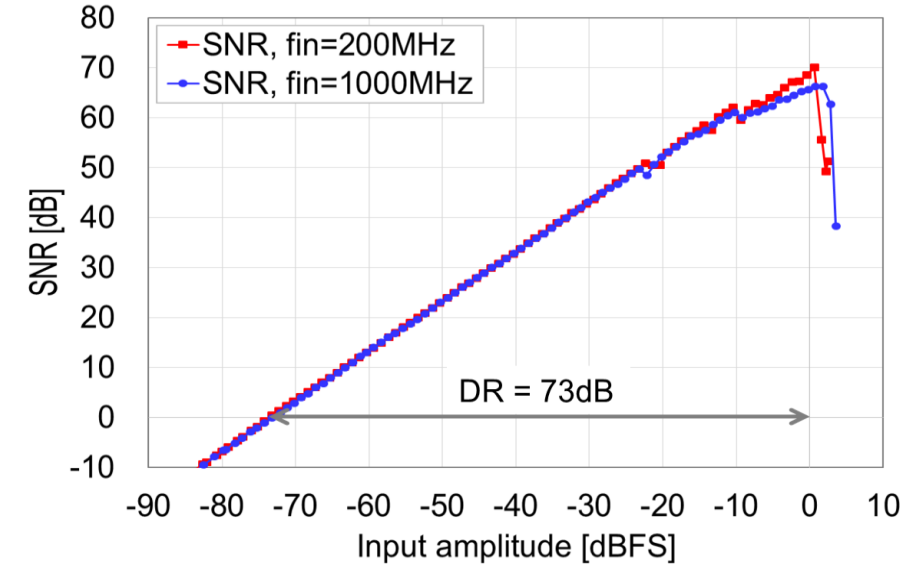
Resolution	12b
F_{SAMPLE}	10GS/s
SNR	56dB
SNDR	55dB
SFDR	66dB
Input fin	4GHz
Power	2.9W
FOMS_HF	147dB
BW	7.4GHz
DR	60dB
NSD_{small-signal}	-157dBFS/Hz
Technology	28nm



CT pipelined ADCs

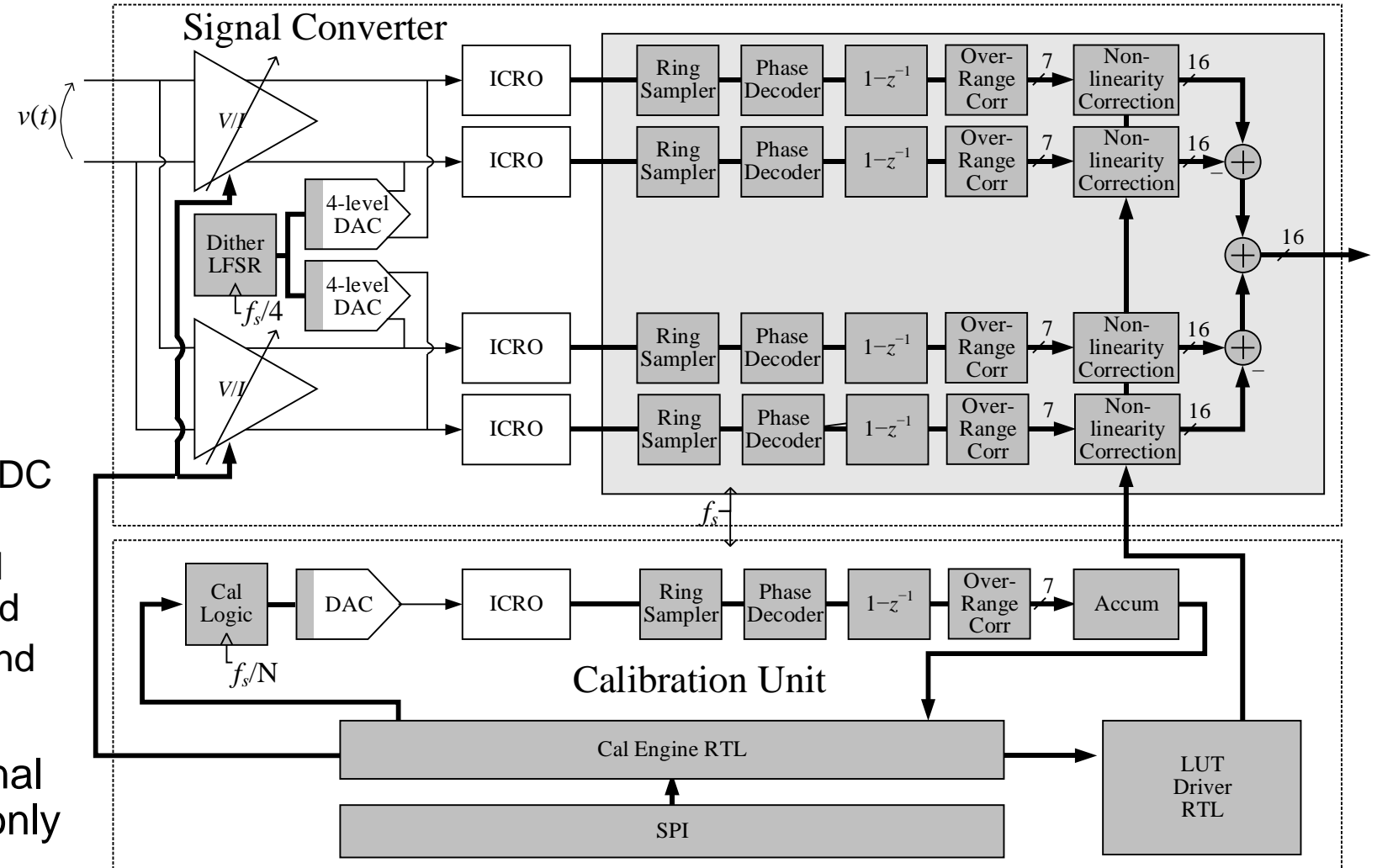


	This work
Architecture	CT pipeline
Inherent Anti-aliasing	Yes
Process Technology	28nm CMOS
f_s [GHz]	9
Raw BW = $f_s / (2 \text{ OSR})$ [MHz]	1125
App BW = $f_s / (2 \text{ App OSR})$ [MHz]	1125
App OSR	4.0
Small-signal NSD = $\text{DR} + 10 \log_{10}(\text{BW})$ [dBFS/Hz]	-164
Large-signal NSD (low f) = $\text{SNR} + 10 \log_{10}(\text{BW})$ [dBFS/Hz]	-160
Large-signal NSD (high f) = $\text{SNR} + 10 \log_{10}(\text{BW})$ [dBFS/Hz]	-156
IM3 [dBFS]	-84
HD2 [dBFS]	-79
HD3 [dBFS]	-86
SFDR [dB]	73
Area [mm ²]	5.1
Power [mW]	2330
$\text{FOM}_s = \text{DR} + 10 \log_{10}(\text{BW}/P)$ [dB]	160



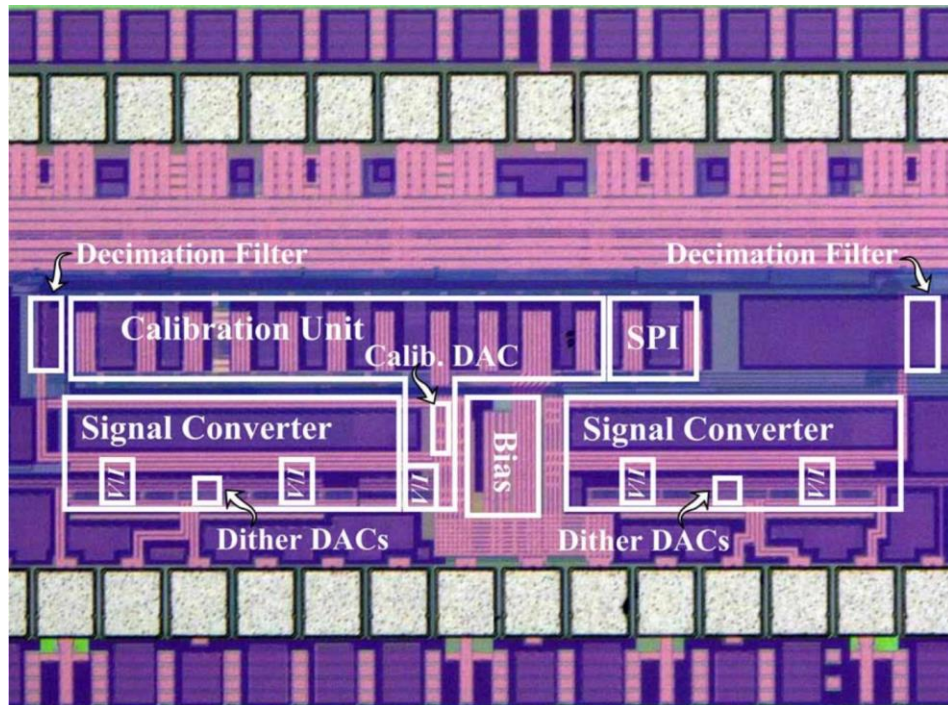
VCOADC

- ▶ Variable gain V/I
- ▶ Reconfigurable
 - $f_s = 1.1\text{-}2.2\text{Gsp}$ s
 - $\text{BW} = 10\text{-}20\text{-}50\text{MHz}$
 - $\text{NSD} = -147\text{ to } -154\text{dBFS}$
 - $\text{Power} = 7\text{-}30\text{mW}/\text{adc}$
- ▶ $\text{SFDR} > 85\text{dBc}$
- ▶ Calibration:
 - Background calibration of replica ADC signal path.
 - All calibration engine logic included with ADC IP, no uController required
 - Continuous calibration or on-demand
 - Calibration period = $15\text{-}30\mu\text{s}$
- ▶ Manual layout for high-speed signal path, P&R for calibration engine only



Why VCOADC?

- ▶ Area is 5-10x smaller than other ADCs with similar specs
- ▶ CT front end-> drive-able
- ▶ Mostly digital->Scalable

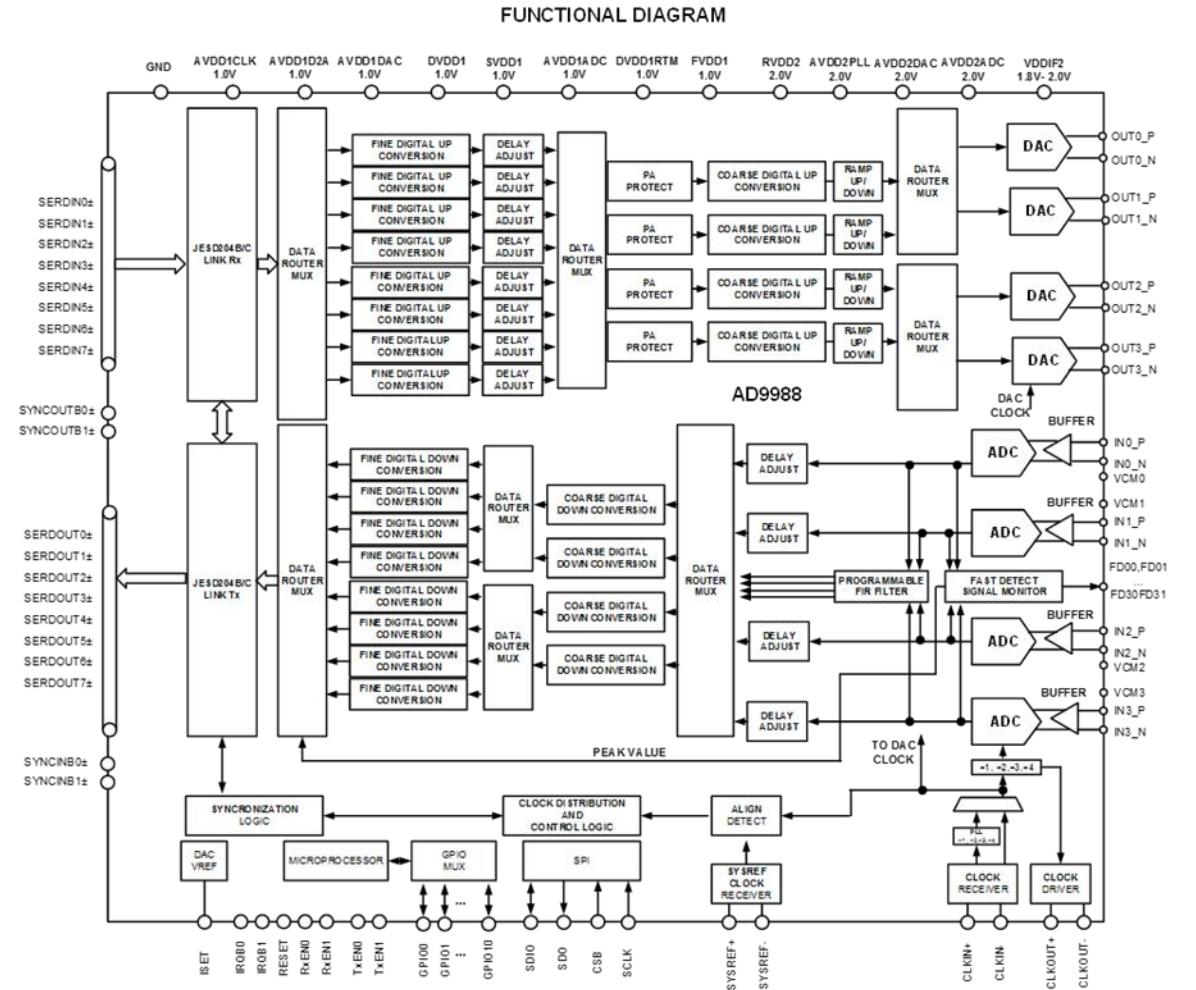
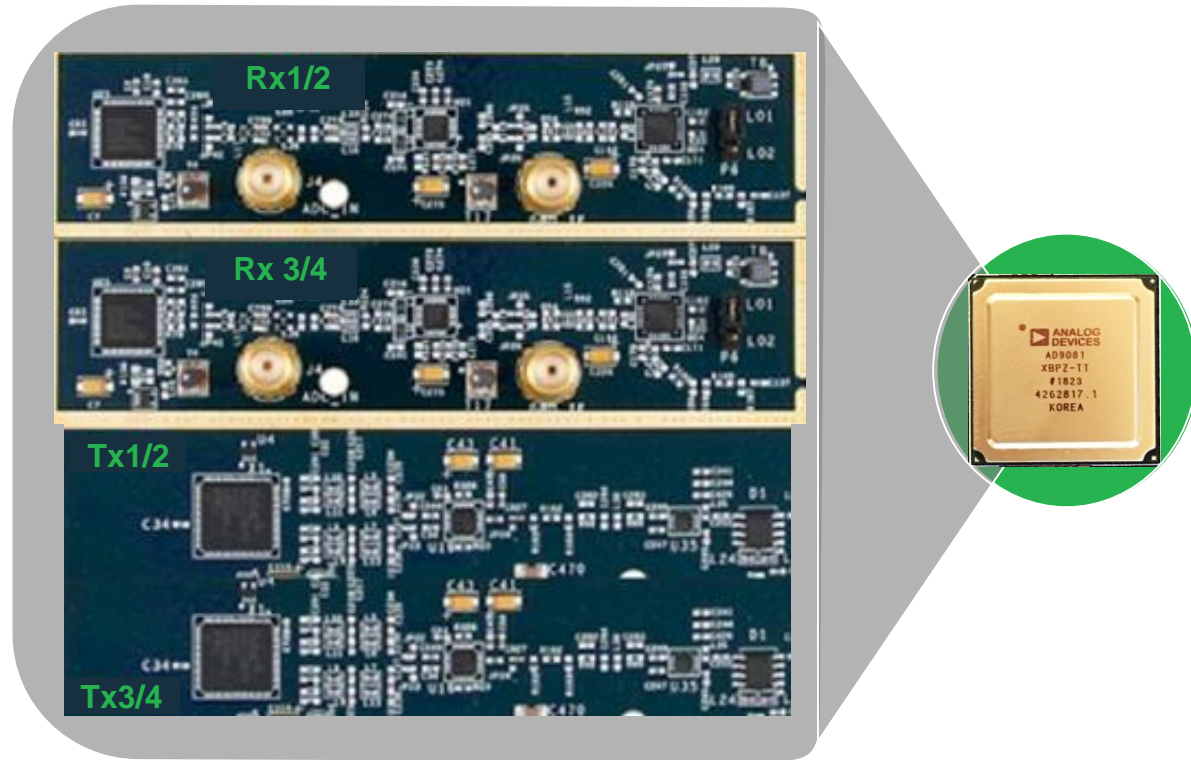




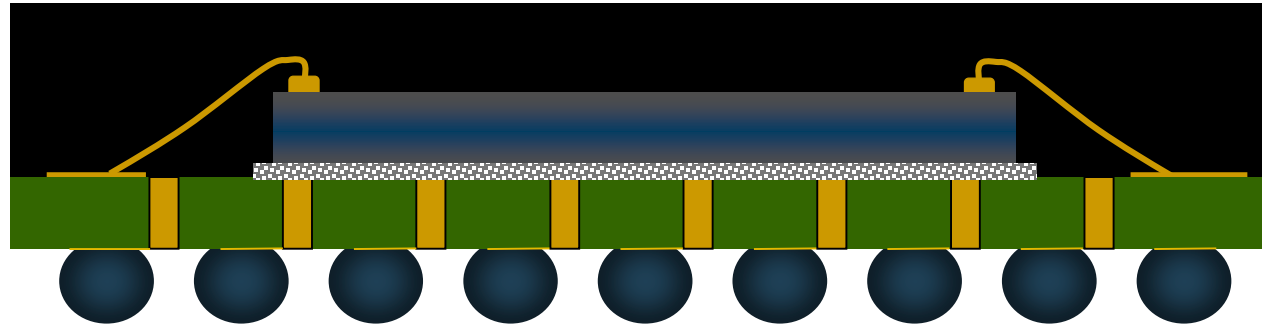
AHEAD OF WHAT'S POSSIBLE™

Integrated Systems: SoCs/SiPs with Mixed-Signal + Embedded DSP Capability

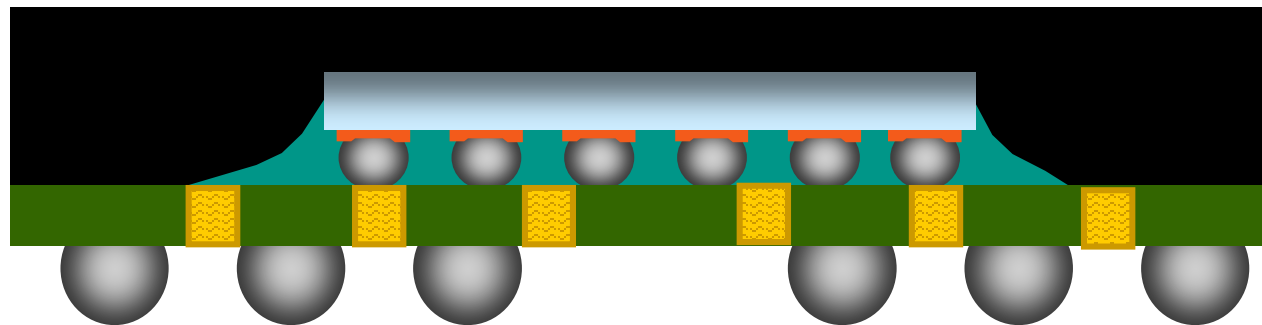
quad Tx / quad-dual Rx fully integrated wideband MxFE



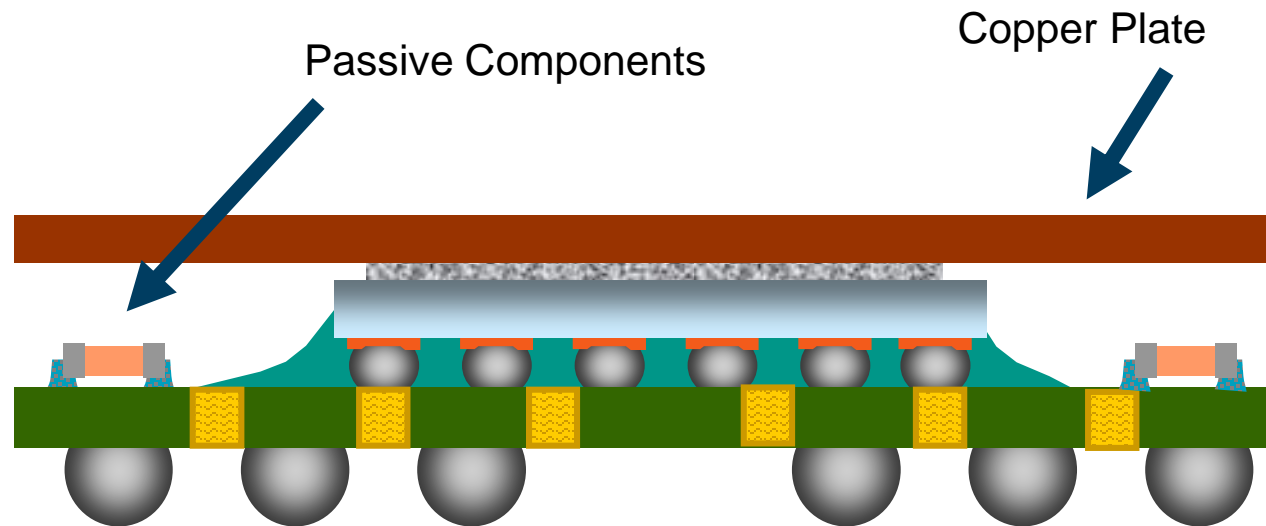
Flip Chip Chip Scale Package BGA



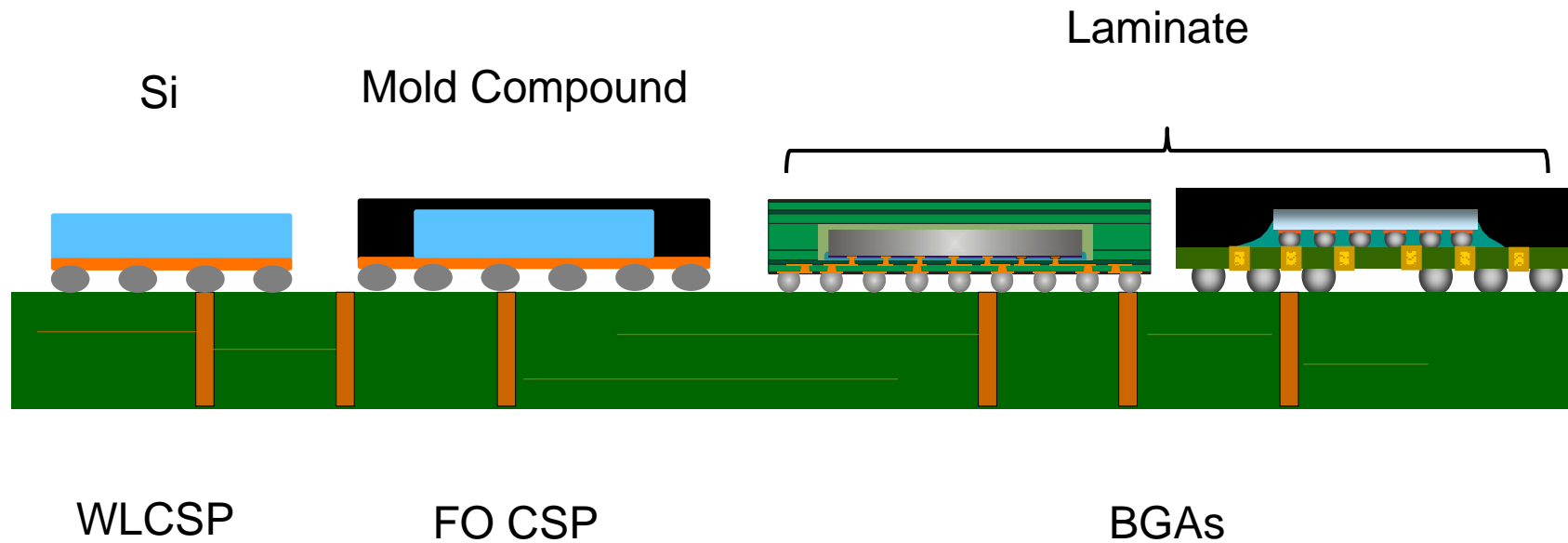
Flip Chip CSP BGA



Flip Chip – Thermally Enhanced BGA



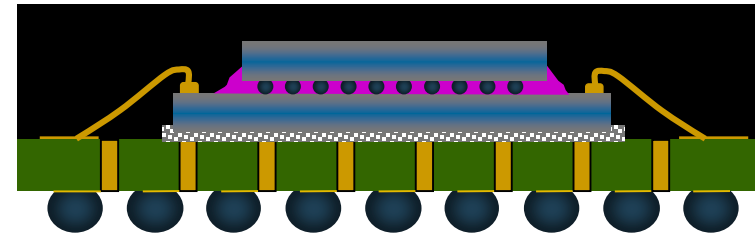
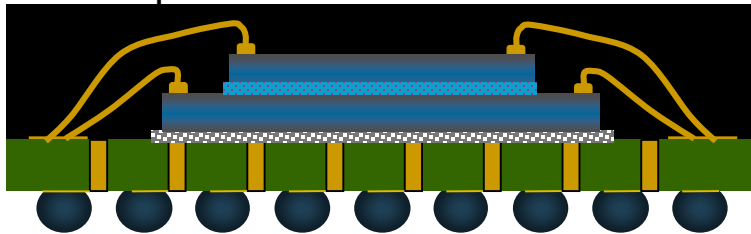
Higher frequency performance



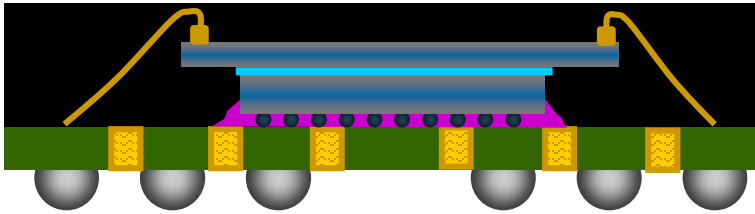
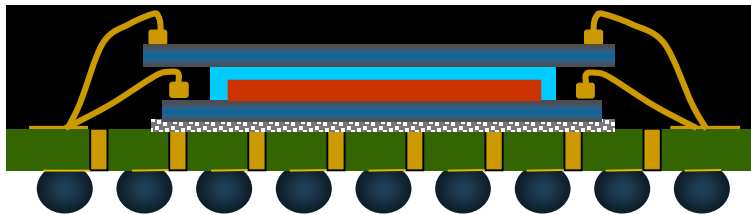
3D Packaging

“Pyramid”

Top Die Smaller Than Bottom



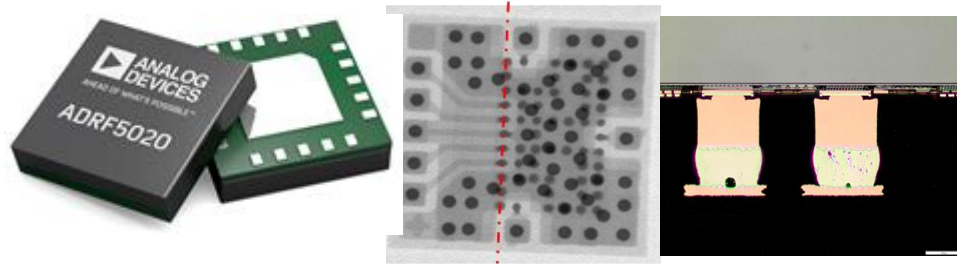
Top Die Same Size or Larger
Than Bottom



Wirebond Versions

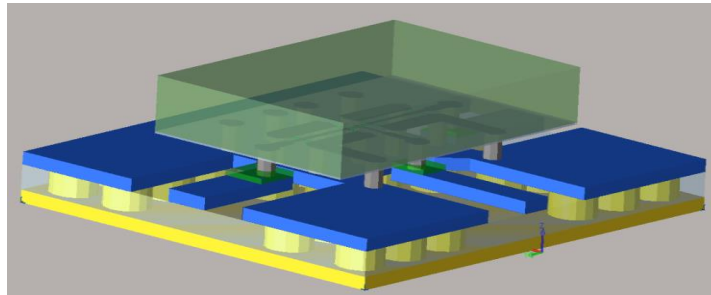
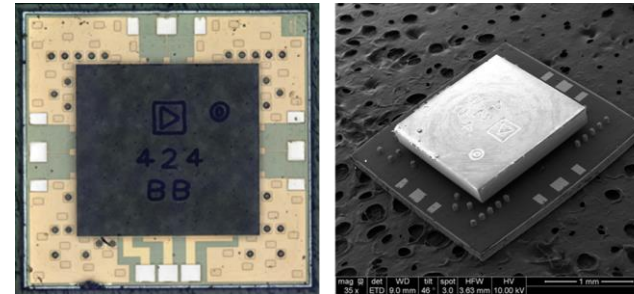
Bumped Die Flip Chip Versions

mmWave front-end modules



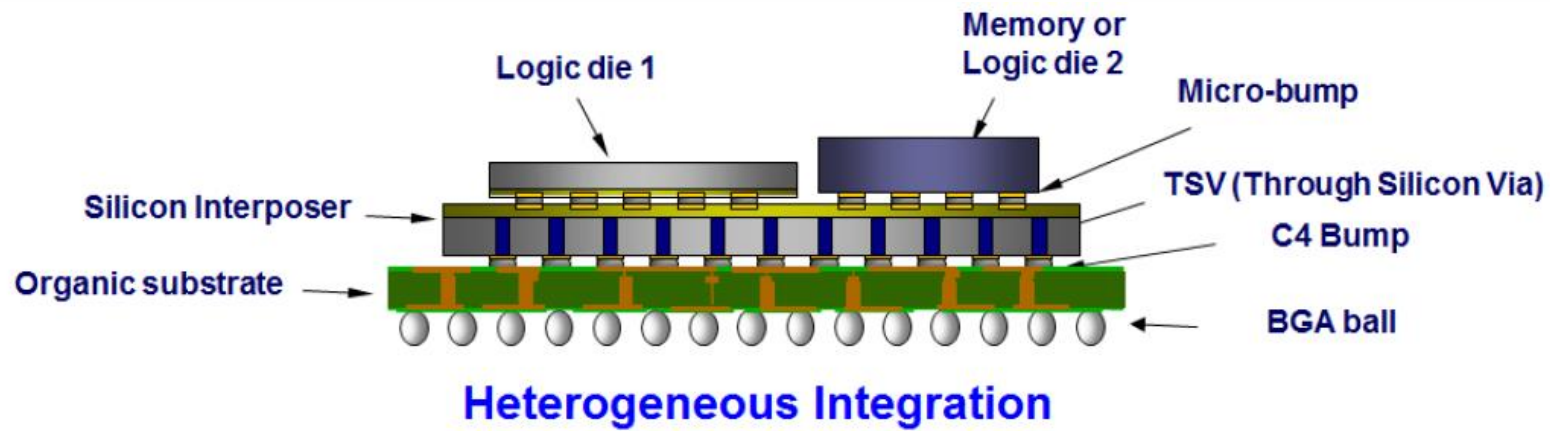
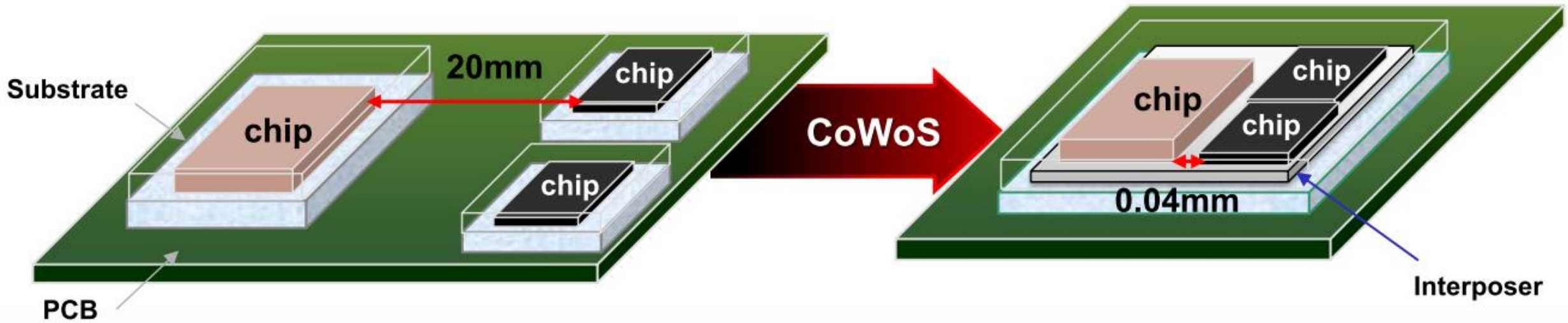
FlipChip on Laminate (LGA)

**Die-On-Carrier (DOC)
“Die-like” RF Product**



**Bumped Flip Chip
(SMT Assembly)**

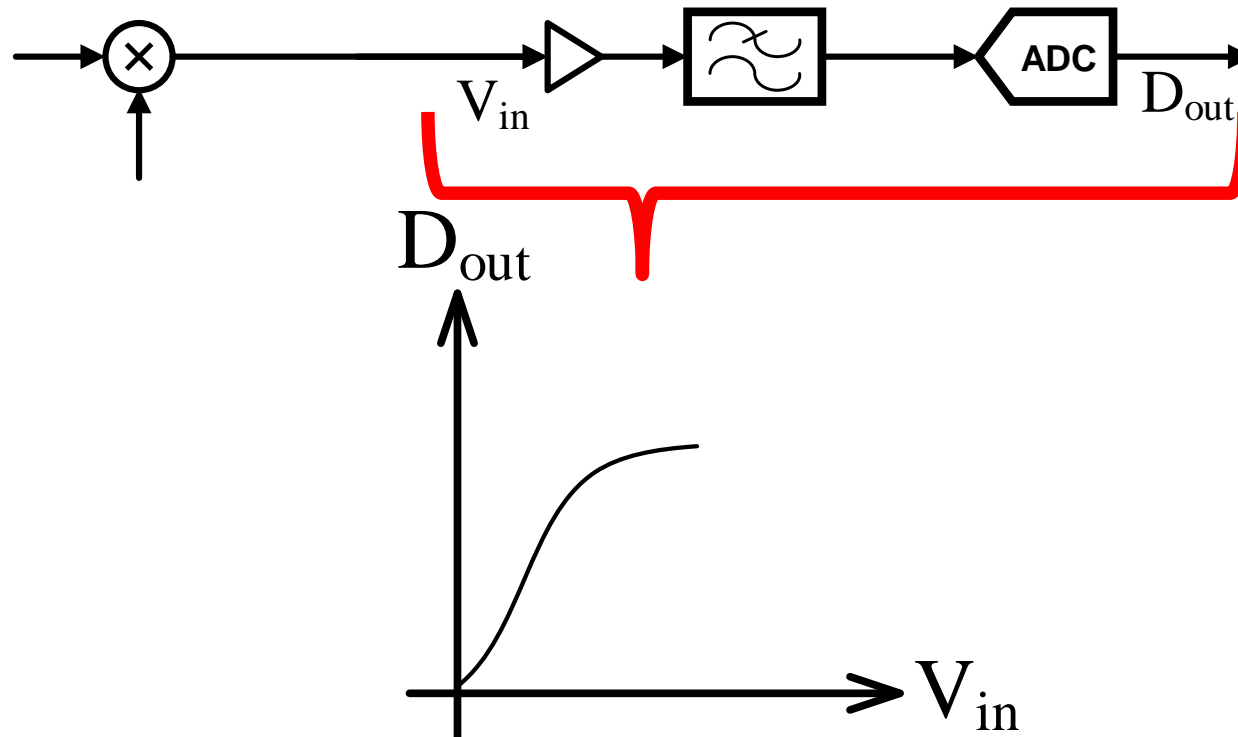
Interposer Systems in a Package



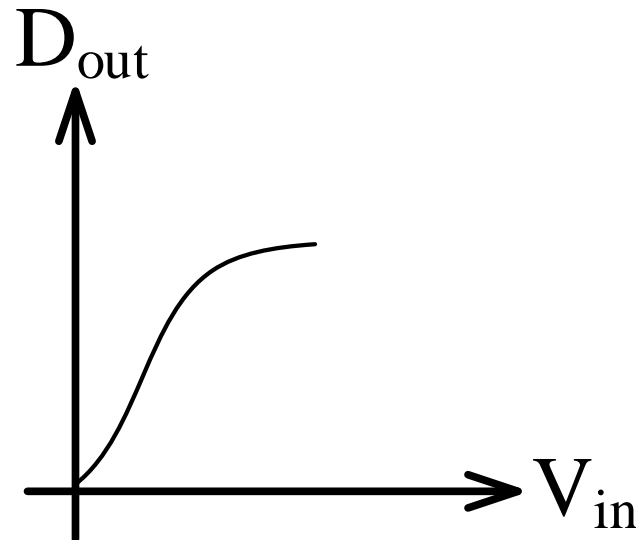
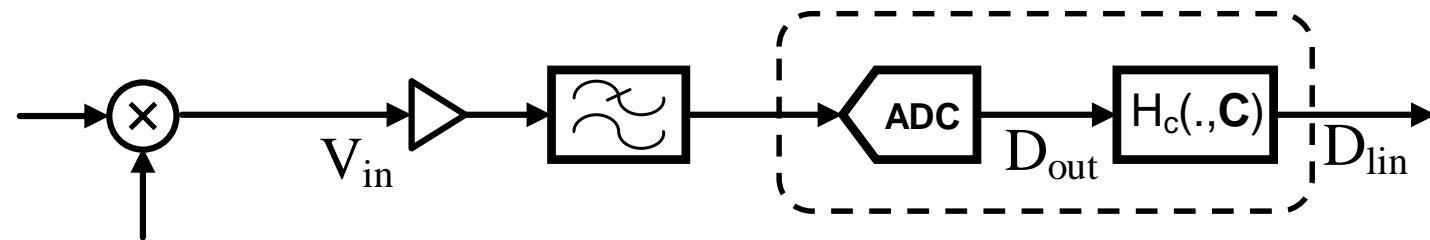
TSMC's CoWoS® (Chip-on-Wafer-on-Substrate) Services, <https://www.tsmc.com/english/dedicatedFoundry/services/cowos.htm>

Algorithmic Capability: System-level Linearization

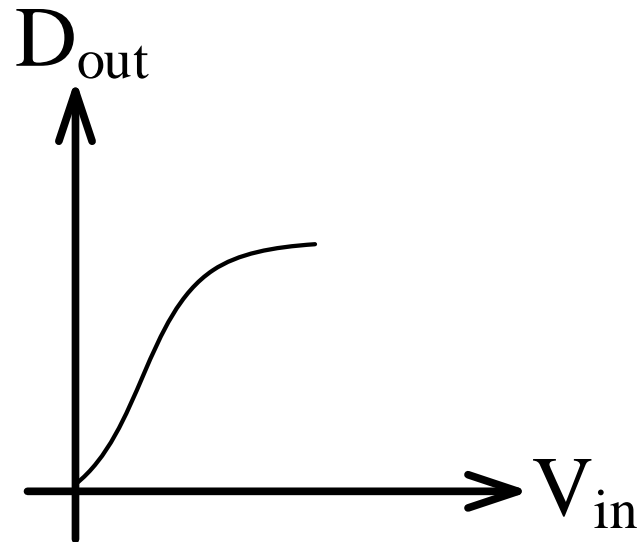
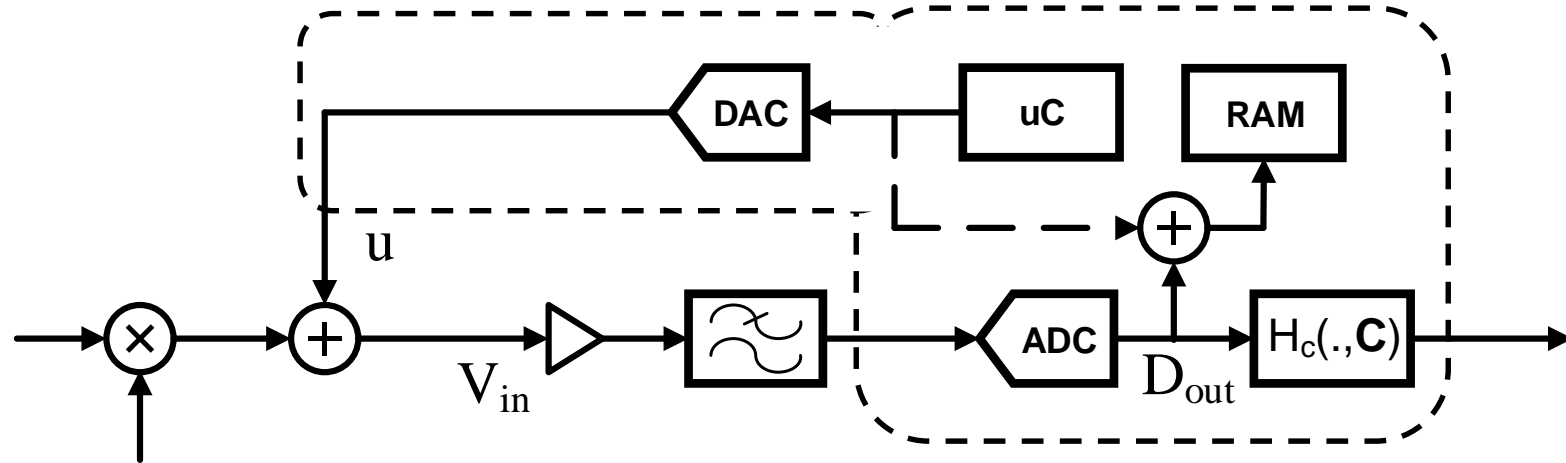
Non-linear Correction for Rx Signal Chain



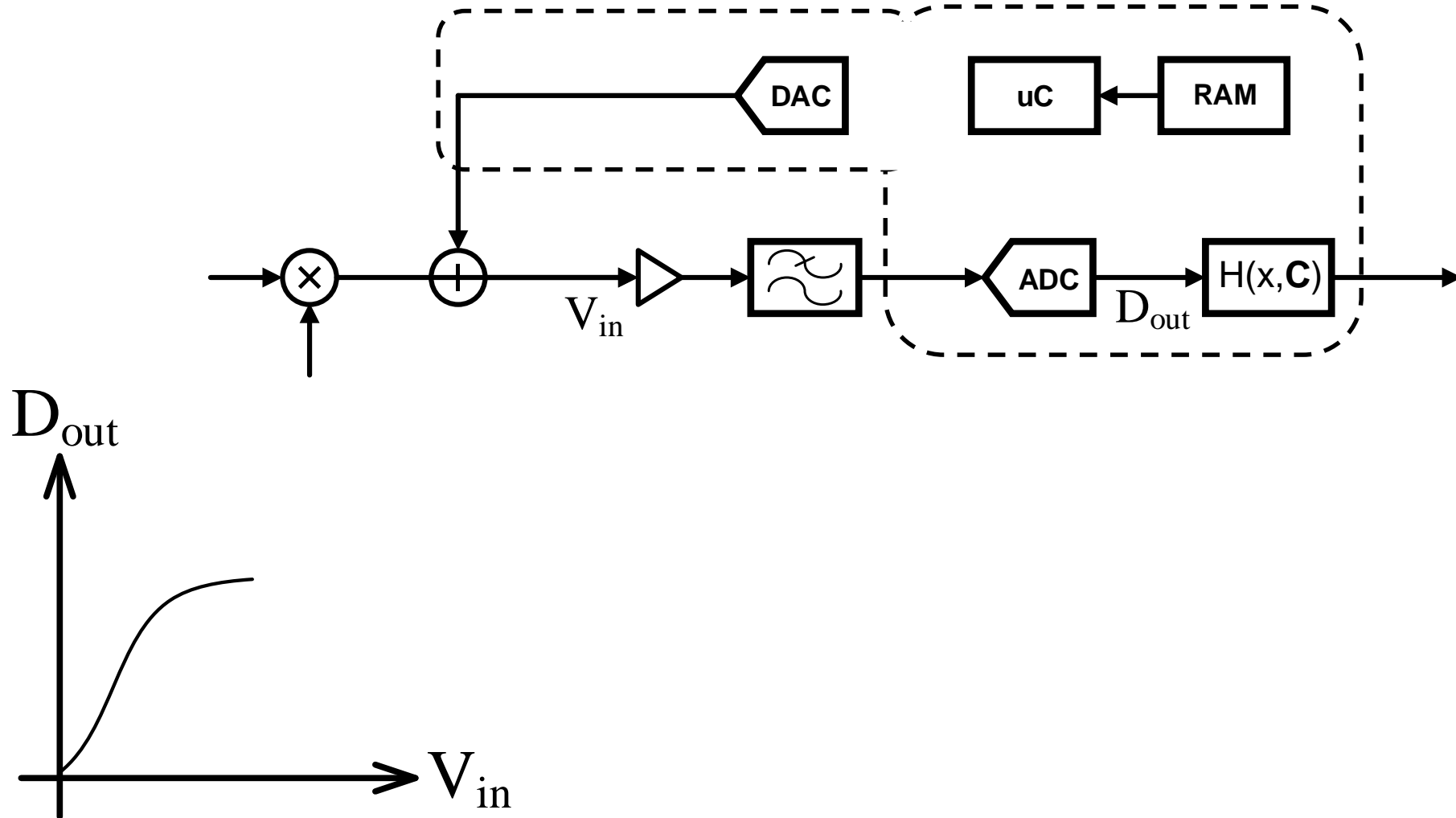
Non-linear Correction for Rx Signal Chain



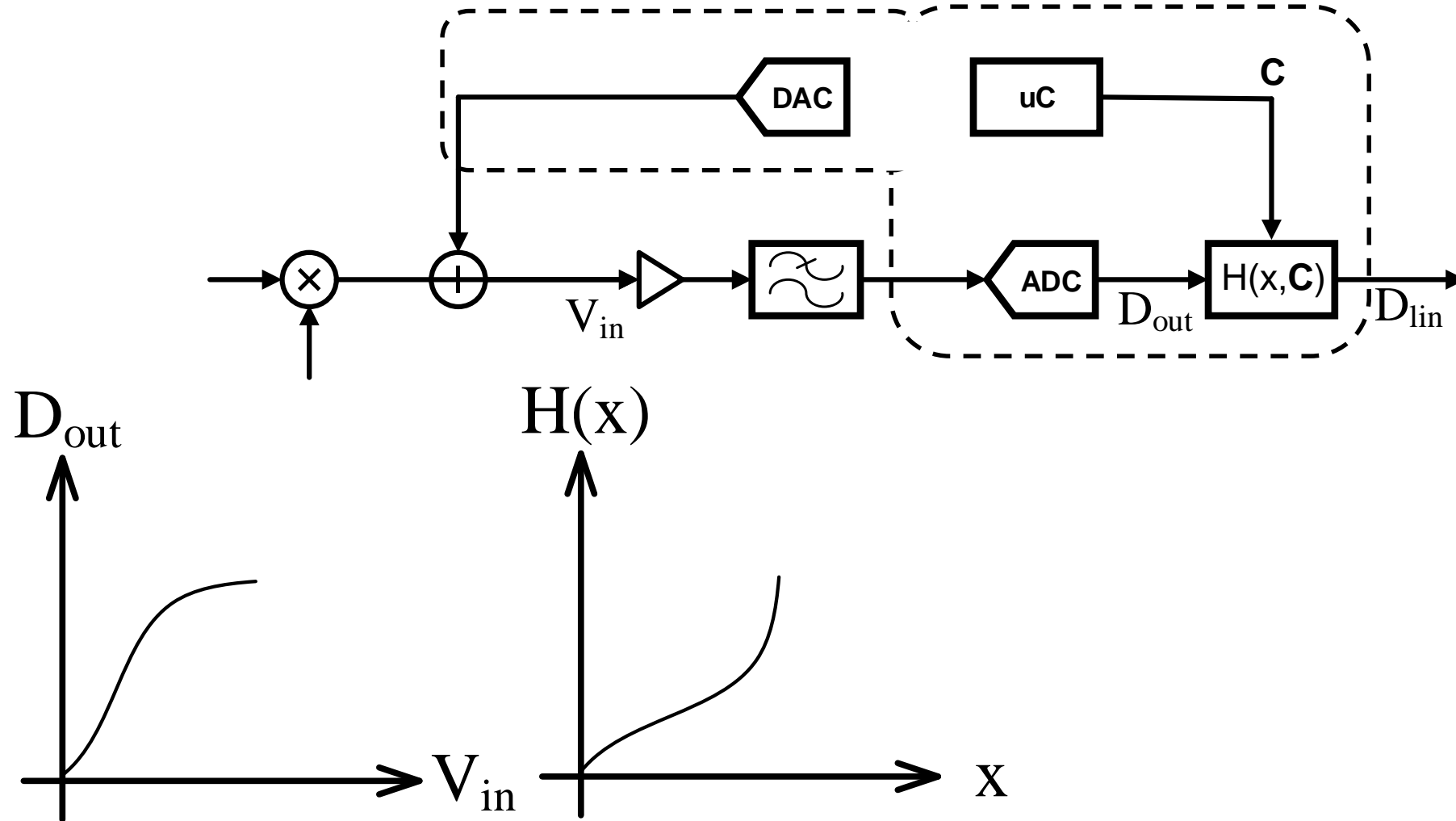
Non-linear Correction for Rx Signal Chain



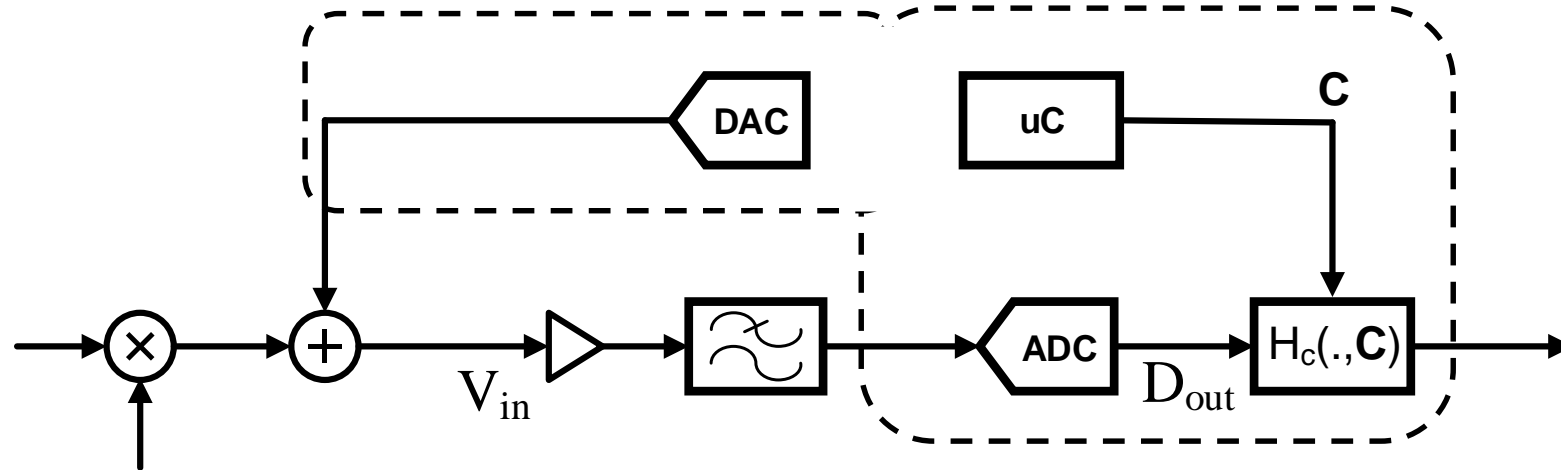
Non-linear Correction for Rx Signal Chain



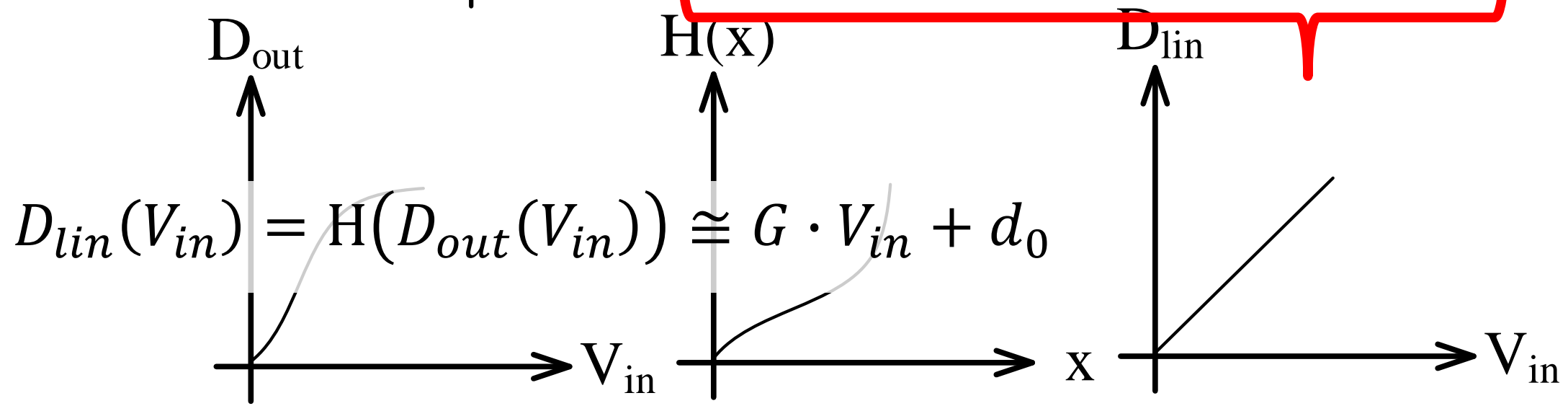
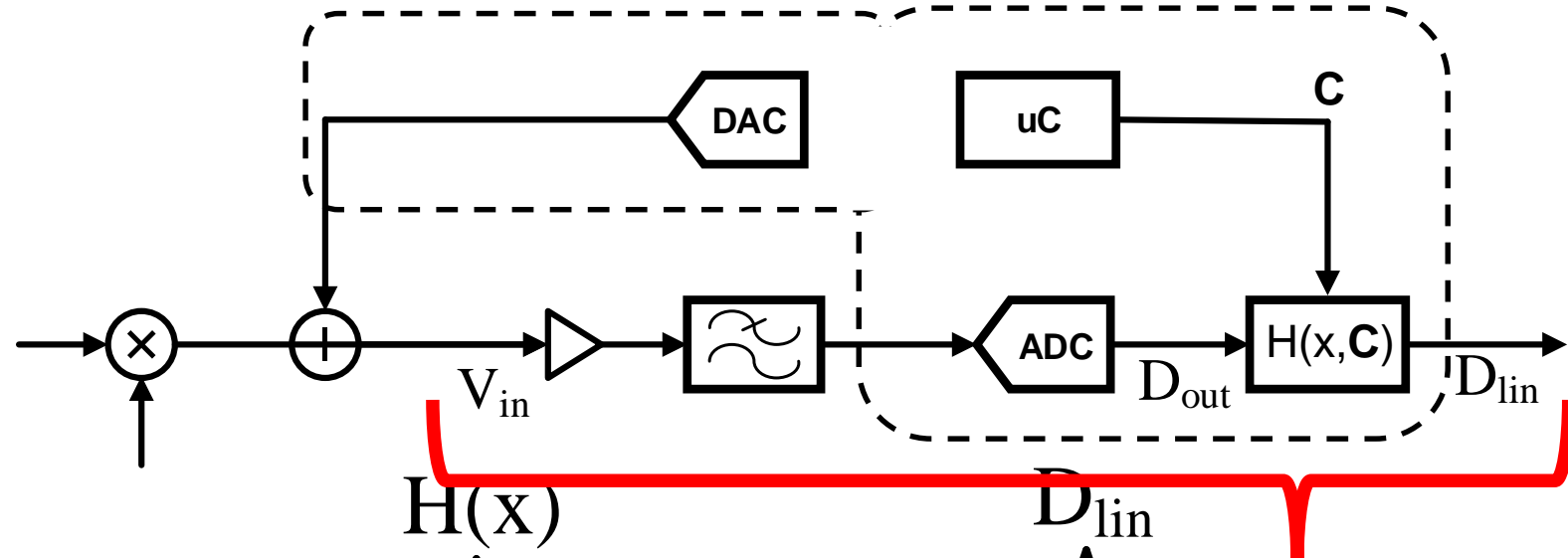
Non-linear Correction for Rx Signal Chain



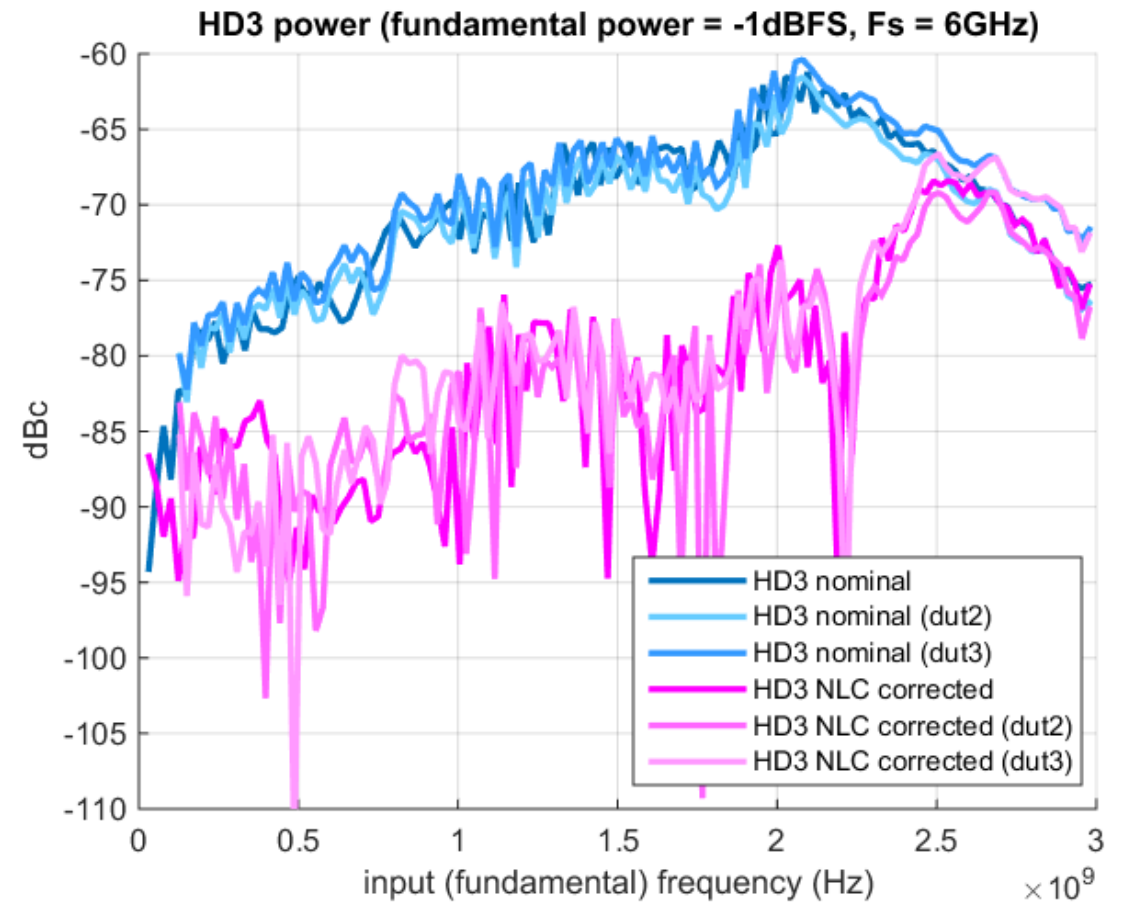
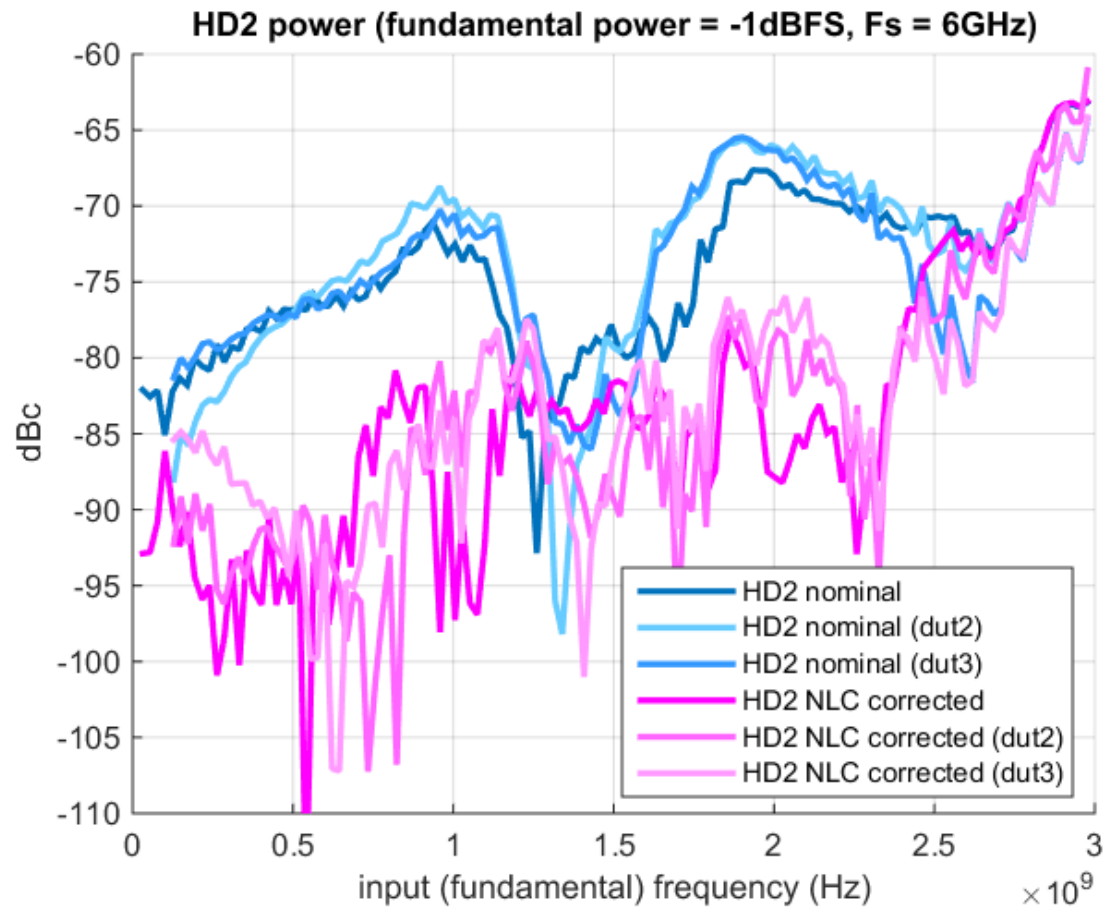
Non-linear Correction for Rx Signal Chain



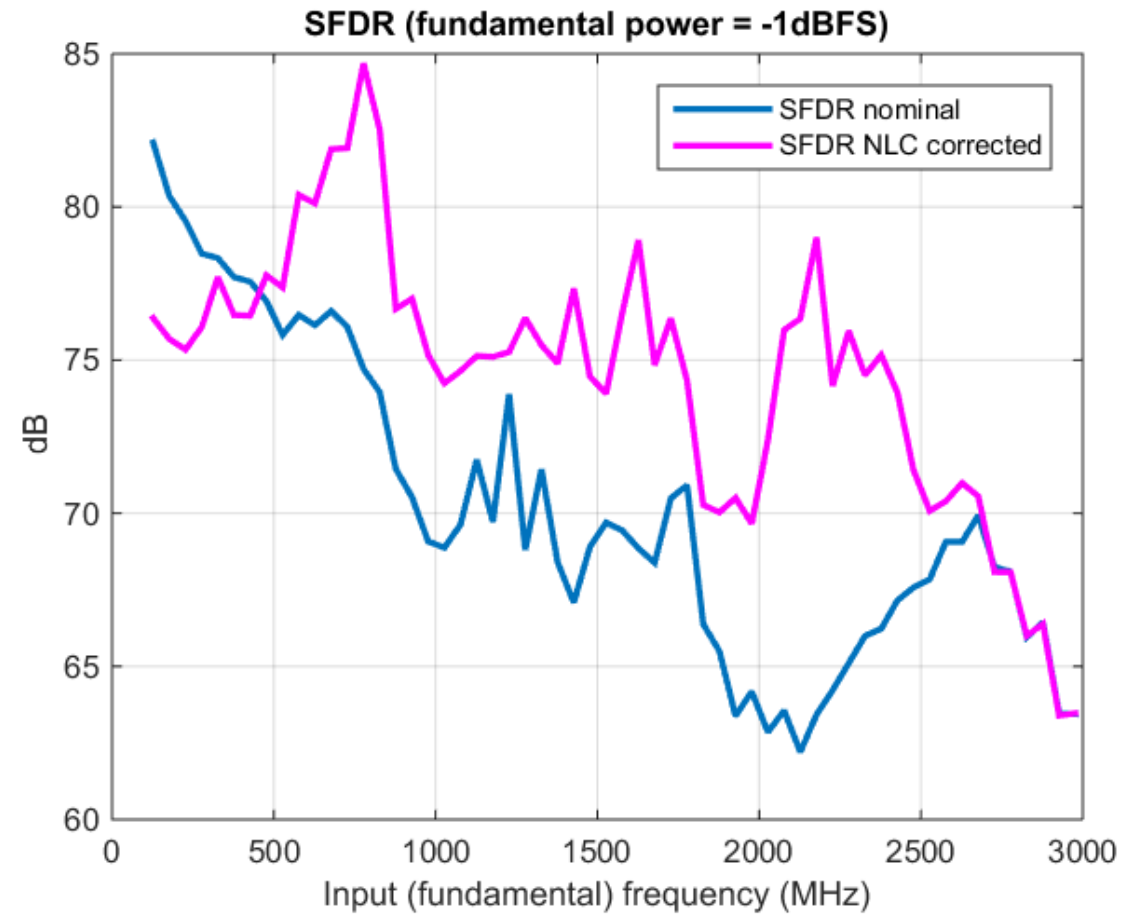
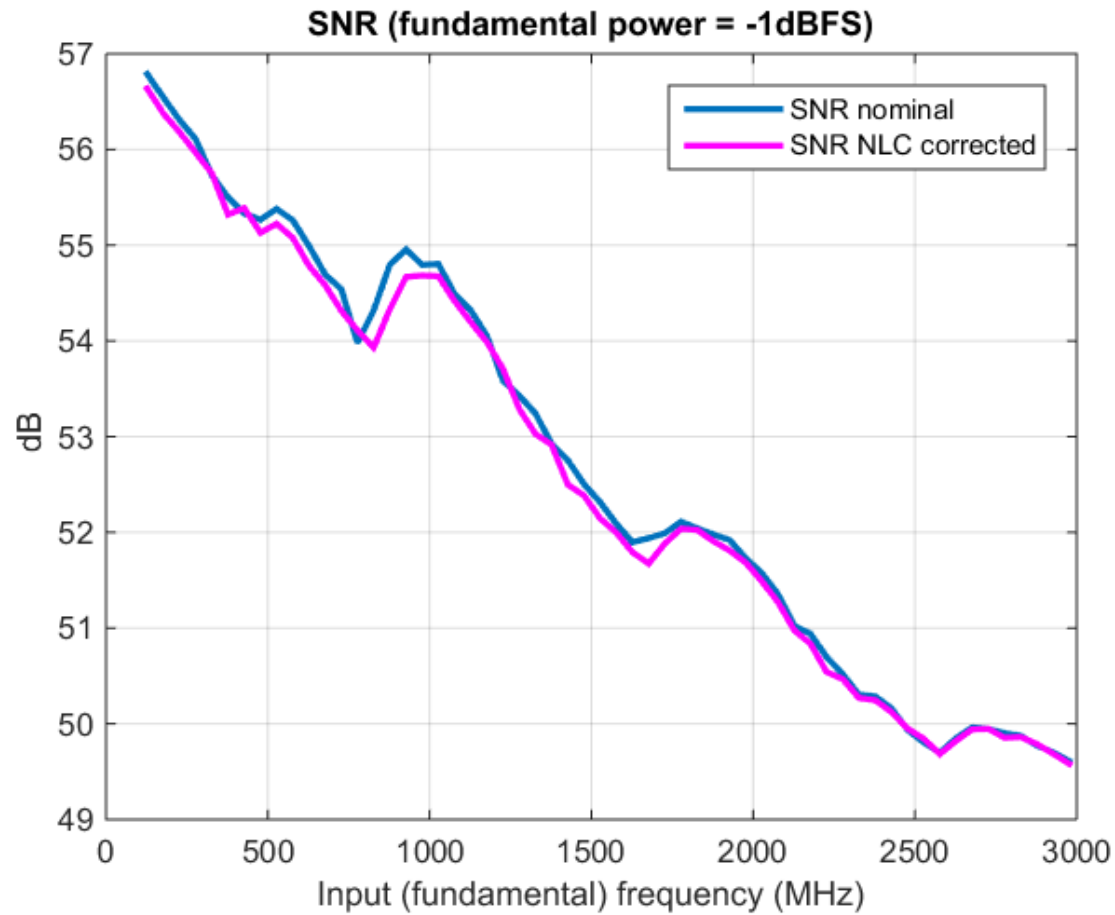
Non-linear Correction for Rx Signal Chain



Fs=6GSPS Lab Data: HD2 & HD3 correction

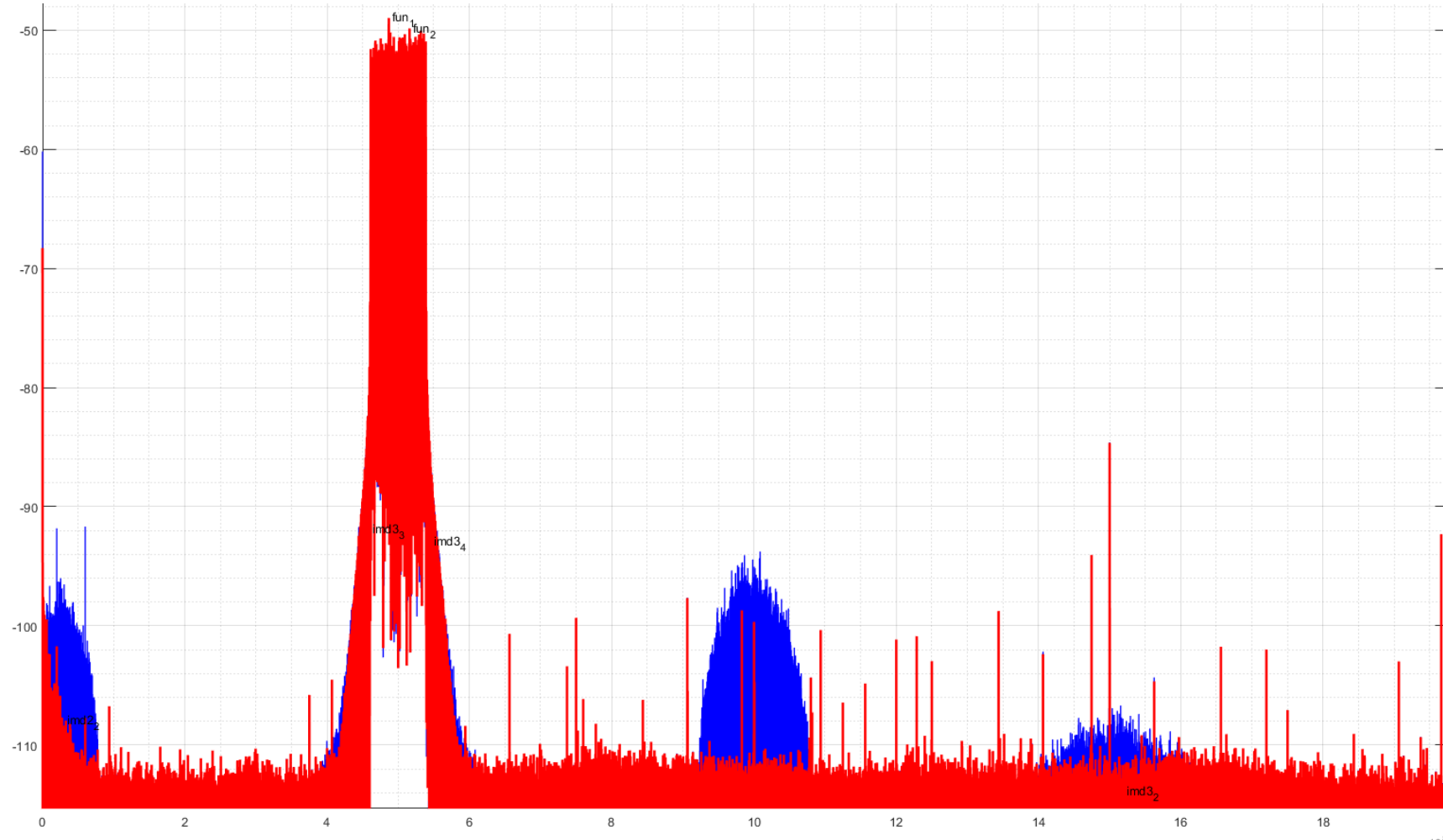


Fs=6GSPS Lab Data: SNR and SFDR



Wi-Fi 6 (802.11AX) Test Signal (500M)

- ▶ Test signal shown at right
- ▶ Before LinearX™ correction in blue
- ▶ After LinearX™ correction in red (tonal spurs are common to both)
- ▶ Training was done using a different wideband training signal spanning 400 – 600M



Conclusion

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A comprehensive approach is required to address the multiple important design constraints:

- Heat removal
- Devices' reliability and aging
- Process technology
- Packaging
- Data interfaces
- Performance/band/power consumption
- Area/costs

QUESTIONS!?

